
BATTERY PROTECTION IC FOR SINGLE-CELL PACK S-8261 Series

The S-8261 series are lithium-ion / lithium polymer rechargeable battery protection ICs incorporating high-accuracy voltage detection circuit and delay circuit.

The S-8261 series are suitable for protection of single-cell lithium ion/lithium polymer battery packs from overcharge, overdischarge and overcurrent.

■ Features

- (1) Internal high accuracy voltage detection circuit
 - Overcharge detection voltage 3.9 V to 4.4 V (applicable in 5 mV step)
Accuracy: ± 25 mV (+25 °C) and ± 30 mV (–5 °C to +55 °C)
 - Overcharge hysteresis voltage 0.0 V to 0.4 V^{*1} Accuracy: ± 25 mV
The overcharge hysteresis voltage can be selected from the range 0.0 V to 0.4 V in 50 mV step.
 - Overdischarge detection voltage 2.0 V to 3.0 V (applicable in 10 mV step) Accuracy: ± 50 mV
 - Overdischarge hysteresis voltage 0.0 V to 0.7 V^{*2} Accuracy: ± 50 mV
The overdischarge hysteresis voltage can be selected from the range 0.0 V to 0.7 V in 100 mV step.
 - Overcurrent 1 detection voltage 0.05 V to 0.3 V (applicable in 10 mV step) Accuracy: ± 15 mV
 - Overcurrent 2 detection voltage 0.5 V (fixed) Accuracy: ± 100 mV
- (2) High voltage device is used for charger connection pins
(VM and CO pins: absolute maximum rating = 28 V)
- (3) Delay times (overcharge: t_{CU} , overdischarge: t_{DL} , overcurrent 1: t_{IOV1} , overcurrent 2: t_{IOV2}) are generated by an internal circuit. No external capacitor is necessary. Accuracy: $\pm 20\%$
- (4) Three-step overcurrent detection circuit is included.
(overcurrent 1, overcurrent 2 and load short-circuiting)
- (5) 0 V battery charge function “available” / “unavailable” are selectable.
- (6) Charger detection function and abnormal charge current detection function
 - The overdischarge hysteresis is released by detecting negative voltage at the VM pin (–0.7 V typ.).
(Charger detection function)
 - When the output voltage of the DO pin is high and the voltage at the VM pin is equal to or lower than the charger detection voltage (–0.7 V typ.), the output voltage of the CO pin goes low. (Abnormal charge current detection function)
- (7) Low current consumption
 - Operation mode 3.5 μ A typ., 7.0 μ A max.
 - Power-down mode 0.1 μ A max.
- (8) Wide operating temperature range –40 °C to +85 °C
- (9) Small package SOT-23-6, 6-Pin SNB(B)

*1. Overcharge release voltage = Overcharge detection voltage – Overcharge hysteresis voltage
(where overcharge release voltage < 3.8 V is prohibited.)

*2. Overdischarge release voltage = Overdischarge detection voltage + Overdischarge hysteresis voltage
(where overdischarge release voltage > 3.4 V is prohibited.)

■ Applications

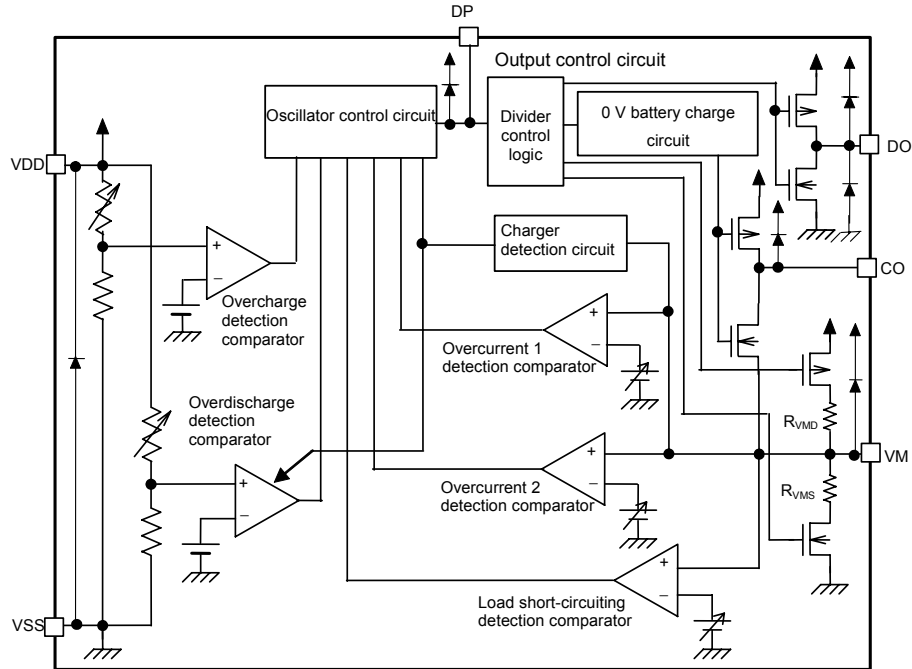
- Lithium-ion rechargeable battery packs
- Lithium polymer rechargeable battery packs

■ Packages

Package name	Drawing code		
	Package	Tape	Reel
SOT-23-6	MP006-A	MP006-A	MP006-A
6-Pin SNB(B)	BD006-A	BD006-A	BD006-A

■ **Block Diagrams**

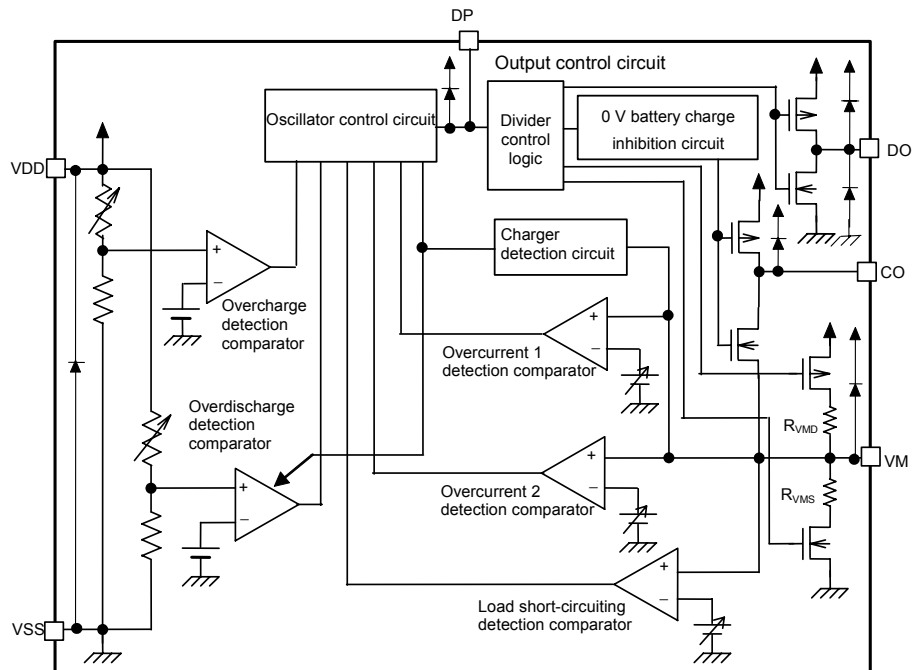
1. Product with 0 V Battery Charge Function



Remark All the diodes shown in the figure are parasitic diodes.

Figure 1

2. Product with 0 V Battery Charge Inhibition Function

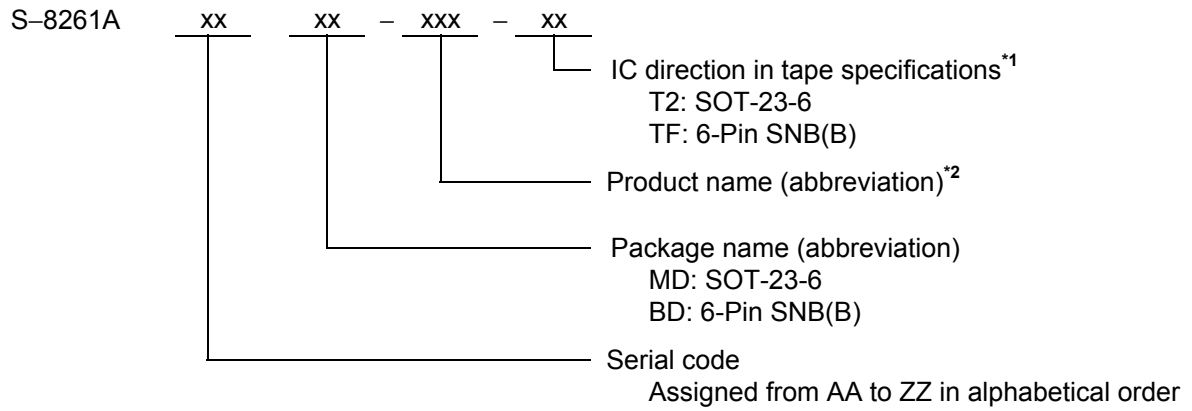


Remark All the diodes shown in the figure are parasitic diodes.

Figure 2

■ **Product Name Structure**

1. Product Name



*1. Refer to the taping specifications.

*2. Refer to the Product Name List.

BATTERY PROTECTION IC FOR SINGLE-CELL PACK

S-8261 Series

Rev.1.9_00

2. Product Name List

Table 1 (1 / 2)

Model No.	Overcharge detection voltage [V _{CU}]	Overcharge hysteresis voltage [V _{HC}]	Overdischarge detection voltage [V _{DL}]	Overdischarge hysteresis voltage [V _{HD}]	Overcurrent 1 detection voltage [V _{IOV1}]	0 V battery charge function
S-8261AAGMD-G2G-T2	4.28 V	0.2 V	2.3 V	0 V	0.16 V	Available
S-8261AAHMD-G2H-T2	4.28 V	0.2 V	2.3 V	0 V	0.08 V	Available
S-8261AAJBD-G2J-TF	4.325 V	0.25 V	2.5 V	0.4 V	0.15 V	Unavailable
S-8261AAJMD-G2J-T2	4.325 V	0.25 V	2.5 V	0.4 V	0.15 V	Unavailable
S-8261AALMD-G2L-T2	4.30 V	0.1 V	2.3 V	0 V	0.08 V	Unavailable
S-8261AAMMD-G2M-T2	4.30 V	0.1 V	2.3 V	0 V	0.2 V	Unavailable
S-8261AANMD-G2N-T2	4.275 V	0.1 V	2.3 V	0.1 V	0.1 V	Available
S-8261AAOMD-G2O-T2	4.28 V	0.2 V	2.3 V	0 V	0.13 V	Unavailable
S-8261AAPMD-G2P-T2	4.325 V	0.25 V	2.5 V	0.4 V	0.1 V	Unavailable
S-8261AARBD-G2R-TF	4.28 V	0.2 V	2.3 V	0 V	0.1 V	Available
S-8261AARMD-G2R-T2	4.28 V	0.2 V	2.3 V	0 V	0.1 V	Available
S-8261AASMD-G2S-T2	4.28 V	0.2 V	2.3 V	0 V	0.15 V	Unavailable
S-8261AAUMD-G2U-T2	4.275 V	0.1 V	2.3 V	0.1 V	0.1 V	Available
S-8261AAVBD-G2V-TF	4.3 V	0.2 V	2.3 V	0 V	0.13 V	Available
S-8261AAXMD-G2X-T2	4.35 V	0.1 V	2.3 V	0.1 V	0.1 V	Available
S-8261AAZMD-G2Z-T2	4.28 V	0.25 V	2.5 V	0.4 V	0.1 V	Unavailable
S-8261ABAMD-G3A-T2	4.35 V	0.2 V	2.5 V	0 V	0.2 V	Available
S-8261ABBMD-G3B-T2	4.275 V	0.2 V	2.3 V	0 V	0.13 V	Available
S-8261ABCMD-G3C-T2	4.30 V	0.2 V	2.3 V	0 V	0.13 V	Available
S-8261ABDBD-G3D-TF	4.28 V	0.2 V	2.3 V	0 V	0.13 V	Available
S-8261ABEBD-G3E-TF	4.275 V	0.2 V	2.3 V	0 V	0.1 V	Available
S-8261ABGBD-G3G-TF	4.275 V	0.2 V	2.3 V	0 V	0.1 V	Unavailable
S-8261ABHBD-G3H-TF	4.20 V	0 V	2.3 V	0 V	0.1 V	Available
S-8261ABIBD-G3I-TF	4.275 V	0.2 V	2.3 V	0 V	0.2 V	Unavailable
S-8261ABJMD-G3J-T2	4.28 V	0.2 V	3.0 V	0 V	0.08 V	Available
S-8261ABKMD-G3K-T2	4.10 V	0.25 V	2.5 V	0.4 V	0.15 V	Unavailable
S-8261ABLBD-G3L-TF	4.275 V	0.2 V	2.3 V	0 V	0.05 V	Unavailable
S-8261ABMMD-G3M-T2	4.28 V	0.2 V	2.8 V	0 V	0.1 V	Available
S-8261ABNMD-G3N-T2	4.30 V	0.2 V	2.3 V	0 V	0.06 V	Available
S-8261ABOBD-G3O-TF	4.28 V	0.2 V	2.3 V	0 V	0.04 V	Available
S-8261ABPMD-G3P-T2	4.20 V	0.1 V	2.8 V	0.1 V	0.15 V	Unavailable
S-8261ABRMD-G3R-T2	4.275 V	0.2 V	2.5 V	0.4 V	0.15 V	Unavailable
S-8261ABSMD-G3S-T2	4.28 V	0.1 V	2.5 V	0.5 V	0.18 V	Unavailable

Table 1 (2 / 2)

Model No.	Overcharge detection delay time	Overdischarge detection delay time	Overcurrent 1 detection delay time
S-8261AAGMD-G2G-T2	1.2 s	144 ms	9 ms
S-8261AAHMD-G2H-T2	1.2 s	144 ms	9 ms
S-8261AAJBD-G2J-TF	1.2 s	144 ms	9 ms
S-8261AAJMD-G2J-T2	1.2 s	144 ms	9 ms
S-8261AALMD-G2L-T2	1.2 s	144 ms	9 ms
S-8261AAMMD-G2M-T2	1.2 s	144 ms	9 ms
S-8261AANMD-G2N-T2	1.2 s	144 ms	9 ms
S-8261AAOMD-G2O-T2	1.2 s	144 ms	9 ms
S-8261AAPMD-G2P-T2	1.2 s	144 ms	9 ms
S-8261AARBD-G2R-TF	1.2 s	144 ms	9 ms
S-8261AARMMD-G2R-T2	1.2 s	144 ms	9 ms
S-8261AASMD-G2S-T2	1.2 s	144 ms	4.5 ms
S-8261AAUMD-G2U-T2	4.6 s	144 ms	9 ms
S-8261AAVBD-G2V-TF	4.6 s	144 ms	9 ms
S-8261AAXMD-G2X-T2	4.6 s	144 ms	9 ms
S-8261AAZMD-G2Z-T2	1.2 s	144 ms	9 ms
S-8261ABAMD-G3A-T2	4.6 s	144 ms	9 ms
S-8261ABBMD-G3B-T2	1.2 s	144 ms	9 ms
S-8261ABCMD-G3C-T2	1.2 s	144 ms	9 ms
S-8261ABDBD-G3D-TF	1.84 s	115 ms	7.2 ms
S-8261ABEBD-G3E-TF	1.2 s	144 ms	9 ms
S-8261ABGBD-G3G-TF	1.2 s	36 ms	9 ms
S-8261ABHBD-G3H-TF	0.3 s	36 ms	18 ms
S-8261ABIBD-G3I-TF	1.2 s	36 ms	9 ms
S-8261ABJMD-G3J-T2	1.2 s	144 ms	9 ms
S-8261ABKMD-G3K-T2	1.2 s	144 ms	9 ms
S-8261ABLBD-G3L-TF	1.2 s	36 ms	9 ms
S-8261ABMMD-G3M-T2	1.2 s	144 ms	9 ms
S-8261ABNMD-G3N-T2	1.2 s	144 ms	9 ms
S-8261ABOBD-G3O-TF	1.2 s	144 ms	9 ms
S-8261ABPMD-G3P-T2	1.2 s	144 ms	9 ms
S-8261ABRMD-G3R-T2	1.2 s	144 ms	9 ms
S-8261ABSMD-G3S-T2	1.2 s	144 ms	9 ms

Remark It is possible to change the detection voltages of the product other than above. The delay times can also be changed within the range listed below. For details, please contact SII marketing department.

Delay time	Symbol	Selection range			Remarks
Overcharge detection delay time	t_{CU}	0.15 s	1.2 s	4.6 s	Choose from the left.
Overdischarge detection delay time	t_{DL}	36 ms	144 ms	290 ms	Choose from the left.
Overcurrent 1 detection delay time	t_{IOV1}	4.5 ms	9 ms	18 ms	Choose from the left.

Remark The values surrounded by bold lines are the delay time of the standard products.

■ Pin Configurations

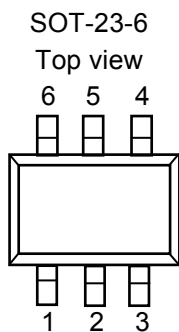
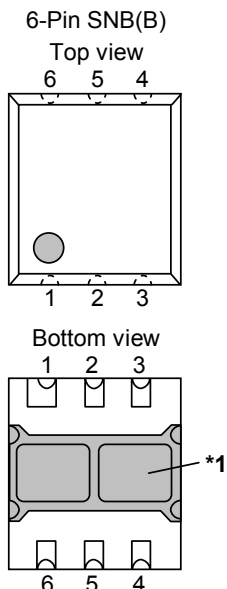


Figure 3

Table 2

Pin No.	Symbol	Pin description
1	DO	FET gate control pin for discharge (CMOS output)
2	VM	Voltage detection pin between VM and VSS (Overcurrent detection pin)
3	CO	FET gate control pin for charge (CMOS output)
4	DP	Test pin for delay time measurement
5	VDD	Positive power input pin
6	VSS	Negative power input pin



*1. Connect the heatsink of back side at shadowed area to the board, and set electric potential open or VDD. However, do not use it as the function of electrode.

Figure 4

Table 3

Pin No.	Symbol	Pin description
1	CO	FET gate control pin for charge (CMOS output)
2	VM	Voltage detection pin between VM and VSS (Overcurrent detection pin)
3	DO	FET gate control pin for discharge (CMOS output)
4	VSS	Negative power input pin
5	DP	Test pin for delay time measurement
6	VDD	Positive power input pin

■ **Absolute Maximum Ratings**

Table 4

(Ta = 25 °C unless otherwise specified)

Parameter		Symbol	Applied pin	Rating	Unit
Input voltage between VDD and VSS*1		V_{DS}	VDD	$V_{SS} - 0.3$ to $V_{SS} + 12$	V
Input pin voltage for VM		V_{VM}	VM	$V_{DD} - 28$ to $V_{DD} + 0.3$	V
Output pin voltage for CO		V_{CO}	CO	$V_{VM} - 0.3$ to $V_{DD} + 0.3$	V
Output pin voltage for DO		V_{DO}	DO	$V_{SS} - 0.3$ to $V_{DD} + 0.3$	V
Power dissipation	SOT-23-6	P_D	—	250	mW
	6-pin SNB(B)	P_D	—	90	mW
Operating temperature range		T_{opr}	—	-40 to +85	°C
Storage temperature range		T_{stg}	—	-55 to +125	°C

Caution The absolute maximum ratings are rated values exceeding which the product could suffer physical damage. These values must therefore not be exceeded under any conditions.

- *1. Even pulse (μ s) noise exceeding the above input voltage ($V_{SS} + 12$ V) may damage the IC, so do not allow such noise to be applied.

BATTERY PROTECTION IC FOR SINGLE-CELL PACK S-8261 Series

Rev.1.9_00

■ Electrical Characteristics

1. Except Detection Delay Time (25 °C)

Table 5

(Ta = 25 °C unless otherwise specified)

Parameter	Symbol	Test condition	Remark	Min.	Typ.	Max.	Unit	Test circuit
[DETECTION VOLTAGE]								
Overcharge detection voltage V _{CU} = 3.9 V to 4.4 V, 5 mV Step	V _{CU}	1	—	V _{CU} -0.025	V _{CU}	V _{CU} +0.025	V	1
			Ta = -5 °C to 55 °C*1	V _{CU} -0.030	V _{CU}	V _{CU} +0.030		
Overcharge hysteresis voltage V _{HC} = 0.0 V to 0.4 V, 50 mV Step	V _{HC}	1	—	V _{HC} -0.025	V _{HC}	V _{HC} +0.025	V	1
Overdischarge detection voltage V _{DL} = 2.0 V to 3.0 V, 10 mV Step	V _{DL}	2	—	V _{DL} -0.050	V _{DL}	V _{DL} +0.050	V	2
Overdischarge hysteresis voltage V _{HD} = 0.0 V to 0.7 V, 100 mV Step	V _{HD}	2	—	V _{HD} -0.050	V _{HD}	V _{HD} +0.050	V	2
Overcurrent 1 detection voltage V _{IOV1} = 0.05 V to 0.3 V, 10 mV Step	V _{IOV1}	3	—	V _{IOV1} -0.015	V _{IOV1}	V _{IOV1} +0.015	V	2
Overcurrent 2 detection voltage	V _{IOV2}	3	—	0.4	0.5	0.6	V	2
Load short-circuiting detection voltage	V _{SHORT}	3	—	0.9	1.2	1.5	V	2
Charger detection voltage	V _{CHA}	4	—	-1.0	-0.7	-0.4	V	2
[INPUT VOLTAGE, OPERATION VOLTAGE]								
Operation voltage between VDD and VSS	V _{DSOP1}	—	Internal circuit operating voltage	1.5	—	8	V	—
Operation voltage between VDD and VM	V _{DSOP2}	—	Internal circuit operating voltage	1.5	—	28	V	—
[CURRENT CONSUMPTION]								
Current consumption in normal operation	I _{OP}	5	V _{DD} = 3.5 V, V _{VM} = 0 V	1.0	3.5	7.0	μA	2
Current consumption at power down	I _{PDN}	5	V _{DD} = V _{VM} = 1.5 V	—	—	0.1	μA	2
[OUTPUT RESISTANCE]								
CO pin resistance "H"	R _{COH}	7	V _{CO} = 3.0 V, V _{DD} = 3.5 V, V _{VM} = 0 V	2.5	5	10	kΩ	4
CO pin resistance "L"	R _{COL}	7	V _{CO} = 0.5 V, V _{DD} = 4.5 V, V _{VM} = 0 V	2.5	5	10	kΩ	4
DO pin resistance "H"	R _{DOH}	8	V _{DO} = 3.0 V, V _{DD} = 3.5 V, V _{VM} = 0 V	2.5	5	10	kΩ	4
DO pin resistance "L"	R _{DOL}	8	V _{DO} = 0.5 V, V _{DD} = V _{VM} = 1.8 V	2.5	5	10	kΩ	4
[VM INTERNAL RESISTANCE]								
Internal resistance between VM and VDD	R _{VMD}	6	V _{DD} = 1.8 V, V _{VM} = 0 V	100	300	900	kΩ	3
Internal resistance between VM and VSS	R _{VMS}	6	V _{DD} = 3.5 V, V _{VM} = 1.0 V	10	20	40	kΩ	3
[0 V BATTERY CHARGING FUNCTION]								
0 V battery charge starting charger voltage	V _{OCHA}	11	0 V battery charging available	1.2	—	—	V	2
0 V battery charge inhibition battery voltage	V _{OINH}	12	0 V battery charging unavailable	—	—	0.5	V	2

*1. Since products are not screened at high and low temperatures, the specification for this temperature range is guaranteed by design, not tested in production.

2. Except Detection Delay Time (–40 to +85 °C*1)

Table 6

(Ta = –40 to +85 °C*1 unless otherwise specified)

Parameter	Symbol	Test condition	Remark	Min.	Typ.	Max.	Unit	Test circuit
[DETECTION VOLTAGE]								
Overcharge detection voltage V _{CU} = 3.9 V to 4.4 V, 5 mV Step	V _{CU}	1	—	V _{CU} –0.055	V _{CU}	V _{CU} +0.040	V	1
Overcharge hysteresis voltage V _{HC} = 0.0 V to 0.4 V, 50 mV Step	V _{HC}	1	—	V _{HC} –0.025	V _{HC}	V _{HC} +0.025	V	1
Overdischarge detection voltage V _{DL} = 2.0 V to 3.0 V, 10 mV Step	V _{DL}	2	—	V _{DL} –0.080	V _{DL}	V _{DL} +0.080	V	2
Overdischarge hysteresis voltage V _{HD} = 0.0 V to 0.7 V, 100 mV Step	V _{HD}	2	—	V _{HD} –0.050	V _{HD}	V _{HD} +0.050	V	2
Overcurrent 1 detection voltage V _{IOV1} = 0.05 V to 0.3 V, 10 mV Step	V _{IOV1}	3	—	V _{IOV1} –0.021	V _{IOV1}	V _{IOV1} +0.021	V	2
Overcurrent 2 detection voltage	V _{IOV2}	3	—	0.37	0.5	0.63	V	2
Load short-circuiting detection voltage	V _{SHORT}	3	—	0.7	1.2	1.7	V	2
Charger detection voltage	V _{CHA}	4	—	–1.2	–0.7	–0.2	V	2
[INPUT VOLTAGE, OPERATION VOLTAGE]								
Operation voltage between VDD and VSS	V _{DSOP1}	—	Internal circuit operating voltage	1.5	—	8	V	—
Operation voltage between VDD and VM	V _{DSOP2}	—	Internal circuit operating voltage	1.5	—	28	V	—
[CURRENT CONSUMPTION]								
Current consumption in normal operation	I _{OPE}	5	V _{DD} = 3.5 V, V _{VM} = 0 V	0.7	3.5	8.0	μA	2
Current consumption at power down	I _{PDN}	5	V _{DD} = V _{VM} = 1.5 V	—	—	0.1	μA	2
[OUTPUT RESISTANCE]								
CO pin resistance “H”	R _{COH}	7	V _{CO} = 3.0 V, V _{DD} = 3.5 V, V _{VM} = 0 V	1.2	5	15	kΩ	4
CO pin resistance “L”	R _{COL}	7	V _{CO} = 0.5 V, V _{DD} = 4.5 V, V _{VM} = 0 V	1.2	5	15	kΩ	4
DO pin resistance “H”	R _{DOH}	8	V _{DO} = 3.0 V, V _{DD} = 3.5 V, V _{VM} = 0 V	1.2	5	15	kΩ	4
DO pin resistance “L”	R _{DOL}	8	V _{DO} = 0.5 V, V _{DD} = V _{VM} = 1.8 V	1.2	5	15	kΩ	4
[VM INTERNAL RESISTANCE]								
Internal resistance between VM and VDD	R _{VMD}	6	V _{DD} = 1.8 V, V _{VM} = 0 V	78	300	1310	kΩ	3
Internal resistance between VM and VSS	R _{VMS}	6	V _{DD} = 3.5 V, V _{VM} = 1.0 V	7.2	20	44	kΩ	3
[0 V BATTERY CHARGING FUNCTION]								
0 V battery charge starting charger voltage	V _{OCHA}	11	0 V battery charging available	1.7	—	—	V	2
0 V battery charge inhibition battery voltage	V _{DINH}	12	0 V battery charging unavailable	—	—	0.3	V	2

*1. Since products are not screened at high and low temperatures, the specification for this temperature range is guaranteed by design, not tested in production.

BATTERY PROTECTION IC FOR SINGLE-CELL PACK

S-8261 Series

Rev.1.9_00

3. Detection Delay Time

Table 7

S-8261AAG, S-8261AAH, S-8261AAJ, S-8261AAL, S-8261AAM, S-8261AAN, S-8261AAO, S-8261AAP, S-8261AAR, S-8261AAZ, S-8261ABB, S-8261ABC, S-8261ABE, S-8261ABJ, S-8261ABK, S-8261ABM, S-8261ABN, S-8261ABO, S-8261ABP, S-8261ABR, S-8261ABS

Parameter	Symbol	Test condition	Remark	Min.	Typ.	Max.	Unit	Test circuit
[DELAY TIME] 25 °C								
Overcharge detection delay time	t _{CU}	9	—	0.96	1.2	1.4	s	5
Overdischarge detection delay time	t _{DL}	9	—	115	144	173	ms	5
Overcurrent 1 detection delay time	t _{IOV1}	10	—	7.2	9	11	ms	5
Overcurrent 2 detection delay time	t _{IOV2}	10	—	1.8	2.24	2.7	ms	5
Load short-circuiting detection delay time	t _{SHORT}	10	—	220	320	380	μs	5
[DELAY TIME] -40 °C to +85 °C^{*1}								
Overcharge detection delay time	t _{CU}	9	—	0.7	1.2	2.0	s	5
Overdischarge detection delay time	t _{DL}	9	—	80	144	245	ms	5
Overcurrent 1 detection delay time	t _{IOV1}	10	—	5	9	15	ms	5
Overcurrent 2 detection delay time	t _{IOV2}	10	—	1.2	2.24	3.8	ms	5
Load short-circuiting detection delay time	t _{SHORT}	10	—	150	320	540	μs	5

*1. Since products are not screened at high and low temperatures, the specification for this temperature range is guaranteed by design, not tested in production.

Table 8

S-8261AAS

Parameter	Symbol	Test condition	Remark	Min.	Typ.	Max.	Unit	Test circuit
[DELAY TIME] 25 °C								
Overcharge detection delay time	t _{CU}	9	—	0.96	1.2	1.4	s	5
Overdischarge detection delay time	t _{DL}	9	—	115	144	173	ms	5
Overcurrent 1 detection delay time	t _{IOV1}	10	—	3.6	4.5	5.4	ms	5
Overcurrent 2 detection delay time	t _{IOV2}	10	—	1.8	2.24	2.7	ms	5
Load short-circuiting detection delay time	t _{SHORT}	10	—	220	320	380	μs	5
[DELAY TIME] -40 °C to +85 °C^{*1}								
Overcharge detection delay time	t _{CU}	9	—	0.7	1.2	2.0	s	5
Overdischarge detection delay time	t _{DL}	9	—	80	144	245	ms	5
Overcurrent 1 detection delay time	t _{IOV1}	10	—	2.5	4.5	7.7	ms	5
Overcurrent 2 detection delay time	t _{IOV2}	10	—	1.2	2.24	3.8	ms	5
Load short-circuiting detection delay time	t _{SHORT}	10	—	150	320	540	μs	5

*1. Since products are not screened at high and low temperatures, the specification for this temperature range is guaranteed by design, not tested in production.

Table 9

S-8261AAU, S-8261AAX, S-8261ABA

Parameter	Symbol	Test condition	Remark	Min.	Typ.	Max.	Unit	Test circuit
[DELAY TIME] 25 °C								
Overcharge detection delay time	t _{CU}	9	—	3.7	4.6	5.5	s	5
Overdischarge detection delay time	t _{DL}	9	—	115	144	173	ms	5
Overcurrent 1 detection delay time	t _{IOV1}	10	—	7.2	9	11	ms	5
Overcurrent 2 detection delay time	t _{IOV2}	10	—	1.8	2.24	2.7	ms	5
Load short-circuiting detection delay time	t _{SHORT}	10	—	220	320	380	μs	5
[DELAY TIME] -40 °C to +85 °C*1								
Overcharge detection delay time	t _{CU}	9	—	2.5	4.6	7.8	s	5
Overdischarge detection delay time	t _{DL}	9	—	80	144	245	ms	5
Overcurrent 1 detection delay time	t _{IOV1}	10	—	5	9	15	ms	5
Overcurrent 2 detection delay time	t _{IOV2}	10	—	1.2	2.24	3.8	ms	5
Load short-circuiting detection delay time	t _{SHORT}	10	—	150	320	540	μs	5

*1. Since products are not screened at high and low temperatures, the specification for this temperature range is guaranteed by design, not tested in production.

Table 10

S-8261AAV

Parameter	Symbol	Test condition	Remark	Min.	Typ.	Max.	Unit	Test circuit
[DELAY TIME] 25 °C								
Overcharge detection delay time	t _{CU}	9	—	3.7	4.6	5.5	s	5
Overdischarge detection delay time	t _{DL}	9	—	115	144	173	ms	5
Overcurrent 1 detection delay time	t _{IOV1}	10	—	7.2	9	11	ms	5
Overcurrent 2 detection delay time	t _{IOV2}	10	—	3.6	4.5	5.4	ms	5
Load short-circuiting detection delay time	t _{SHORT}	10	—	450	600	720	μs	5
[DELAY TIME] -40 °C to +85 °C*1								
Overcharge detection delay time	t _{CU}	9	—	2.5	4.6	7.8	s	5
Overdischarge detection delay time	t _{DL}	9	—	80	144	245	ms	5
Overcurrent 1 detection delay time	t _{IOV1}	10	—	5	9	15	ms	5
Overcurrent 2 detection delay time	t _{IOV2}	10	—	2.5	4.5	7.7	ms	5
Load short-circuiting detection delay time	t _{SHORT}	10	—	310	600	1020	μs	5

*1. Since products are not screened at high and low temperatures, the specification for this temperature range is guaranteed by design, not tested in production.

BATTERY PROTECTION IC FOR SINGLE-CELL PACK
S-8261 Series

Rev.1.9_00

Table 11

S-8261ABD

Parameter	Symbol	Test condition	Remark	Min.	Typ.	Max.	Unit	Test circuit
[DELAY TIME] 25°C								
Overcharge detection delay time	t _{CU}	9	—	1.48	1.84	2.2	s	5
Overdischarge detection delay time	t _{DL}	9	—	92	115	138	ms	5
Overcurrent 1 detection delay time	t _{OV1}	10	—	5.76	7.2	8.8	ms	5
Overcurrent 2 detection delay time	t _{OV2}	10	—	2.88	3.6	4.32	ms	5
Load short-circuiting detection delay time	t _{SHORT}	10	—	358	488	586	μs	5
[DELAY TIME] -40°C to +85°C^{*1}								
Overcharge detection delay time	t _{CU}	9	—	1.11	1.84	2.89	s	5
Overdischarge detection delay time	t _{DL}	9	—	68.9	115	182.3	ms	5
Overcurrent 1 detection delay time	t _{OV1}	10	—	4.31	7.2	11.59	ms	5
Overcurrent 2 detection delay time	t _{OV2}	10	—	2.16	3.6	5.68	ms	5
Load short-circuiting detection delay time	t _{SHORT}	10	—	268	488	770	μs	5

*1. Since products are not screened at high and low temperatures, the specification for this temperature range is guaranteed by design, not tested in production.

Table 12

S-8261ABG, S-8261ABI, S-8261ABL

Parameter	Symbol	Test condition	Remark	Min.	Typ.	Max.	Unit	Test circuit
[DELAY TIME] 25°C								
Overcharge detection delay time	t _{CU}	9	—	0.96	1.2	1.4	s	5
Overdischarge detection delay time	t _{DL}	9	—	29	36	43	ms	5
Overcurrent 1 detection delay time	t _{OV1}	10	—	7.2	9	11	ms	5
Overcurrent 2 detection delay time	t _{OV2}	10	—	1.8	2.24	2.7	ms	5
Load short-circuiting detection delay time	t _{SHORT}	10	—	220	320	380	μs	5
[DELAY TIME] -40°C to +85°C^{*1}								
Overcharge detection delay time	t _{CU}	9	—	0.7	1.2	2.0	s	5
Overdischarge detection delay time	t _{DL}	9	—	20	36	61	ms	5
Overcurrent 1 detection delay time	t _{OV1}	10	—	5	9	15	ms	5
Overcurrent 2 detection delay time	t _{OV2}	10	—	1.2	2.24	3.8	ms	5
Load short-circuiting detection delay time	t _{SHORT}	10	—	150	320	540	μs	5

*1. Since products are not screened at high and low temperatures, the specification for this temperature range is guaranteed by design, not tested in production.

Table 13

S-8261ABH

Parameter	Symbol	Test condition	Remark	Min.	Typ.	Max.	Unit	Test circuit
[DELAY TIME] 25°C								
Overcharge detection delay time	t_{CU}	9	—	0.24	0.3	0.36	s	5
Overdischarge detection delay time	t_{DL}	9	—	29	36	43	ms	5
Overcurrent 1 detection delay time	t_{IOV1}	10	—	14	18	22	ms	5
Overcurrent 2 detection delay time	t_{IOV2}	10	—	1.8	2.24	2.7	ms	5
Load short-circuiting detection delay time	t_{SHORT}	10	—	220	320	380	μs	5
[DELAY TIME] -40°C to +85°C^{*1}								
Overcharge detection delay time	t_{CU}	9	—	0.17	0.3	0.51	s	5
Overdischarge detection delay time	t_{DL}	9	—	20	36	61	ms	5
Overcurrent 1 detection delay time	t_{IOV1}	10	—	10	18	31	ms	5
Overcurrent 2 detection delay time	t_{IOV2}	10	—	1.2	2.24	3.8	ms	5
Load short-circuiting detection delay time	t_{SHORT}	10	—	150	320	540	μs	5

*1. Since products are not screened at high and low temperatures, the specification for this temperature range is guaranteed by design, not tested in production.

■ Test Circuits

Remark Unless otherwise specified, the output voltage levels “H” and “L” at CO pin (V_{CO}) and DO pin (V_{DO}) are judged by the threshold voltage (1.0 V) of the N-channel FET. Judge the CO pin level with respect to V_{VM} and the DO pin level with respect to V_{SS} .

(1) Test Condition 1, Test Circuit 1

《Overcharge Detection Voltage, Overcharge Hysteresis Voltage》

The overcharge detection voltage (V_{CU}) is defined by the voltage between VDD and VSS at which V_{CO} goes from “H” to “L” when the voltage $V1$ is gradually increased from the starting condition of $V1 = 3.5$ V. The overcharge hysteresis voltage (V_{HC}) is then defined as the difference between the overcharge detection voltage (V_{CU}) and the voltage between VDD and VSS at which V_{CO} goes from “H” to “L” when the voltage $V1$ is gradually decreased.

(2) Test Condition 2, Test Circuit 2

《Overdischarge Detection Voltage, Overdischarge Hysteresis Voltage》

The overdischarge detection voltage (V_{DL}) is defined as the voltage between VDD and VSS at which V_{DO} goes from “H” to “L” when the voltage $V1$ is gradually decreased from the starting condition of $V1 = 3.5$ V and $V2 = 0$ V. The overdischarge hysteresis voltage (V_{HD}) is then defined as the difference between the overdischarge detection voltage (V_{DL}) and the voltage between VDD and VSS at which V_{DO} goes from “H” to “L” when the voltage $V1$ is gradually increased.

(3) Test Condition 3, Test Circuit 2

《Overcurrent 1 Detection Voltage, Overcurrent 2 Detection Voltage, Load Short-Circuiting Detection Voltage》

The overcurrent 1 detection voltage (V_{IOV1}) is defined as the voltage between VM and VSS whose delay time for changing V_{DO} from “H” to “L” lies between the minimum and the maximum value of the overcurrent 1 detection delay time when the voltage $V2$ is increased rapidly (within 10 μ s) from the starting condition $V1 = 3.5$ V and $V2 = 0$ V.

The overcurrent 2 detection voltage (V_{IOV2}) is defined as the voltage between VM and VSS whose delay time for changing V_{DO} from “H” to “L” lies between the minimum and the maximum value of the overcurrent 2 detection delay time when the voltage $V2$ is increased rapidly (within 10 μ s) from the starting condition $V1 = 3.5$ V and $V2 = 0$ V.

The load short-circuiting detection voltage (V_{SHORT}) is defined as the voltage between VM and VSS whose delay time for changing V_{DO} from “H” to “L” lies between the minimum and the maximum value of the load short-circuiting detection delay time when the voltage $V2$ is increased rapidly (within 10 μ s) from the starting condition $V1 = 3.5$ V and $V2 = 0$ V.

(4) Test Condition 4, Test Circuit 2

《Charger Detection Voltage, Abnormal Charge Current Detection Voltage》

The charger detection voltage (V_{CHA}) is defined as the voltage between VM and VSS at which V_{DO} goes from “L” to “H” when the voltage $V3$ is gradually decreased from 0 V after the voltage $V1$ is gradually increased from the starting condition of $V1 = 1.8$ V and $V2 = 0$ V until the voltage $V1$ becomes $V1 = V_{DL} + (V_{HD} / 2)$.

The charger detection voltage can be measured only in the product whose overdischarge hysteresis $V_{HD} \neq 0$. Set $V1 = 3.5$ V and $V2 = 0$ V. Decrease $V2$ from 0 V gradually. The voltage between VM and VSS when V_{CO} goes from “H” to “L” is the abnormal charge current detection voltage. The abnormal charge current detection voltage has the same value as the charger detection voltage (V_{CHA}).

(5) Test Condition 5, Test Circuit 2

《Normal Operation Current Consumption, Power-Down Current Consumption》

The operating current consumption (I_{OPE}) is the current that flows through the VDD pin (I_{DD}) under the set conditions of $V1 = 3.5$ V and $V2 = 0$ V (Normal condition).

The power-down current consumption (I_{PDN}) is the current that flows through the VDD pin (I_{DD}) under the set conditions of $V1 = V2 = 1.5$ V (Overdischarge condition).

(6) Test Condition 6, Test Circuit 3

《 Internal Resistance between VM and VDD, Internal Resistance between VM and VSS 》

The resistance between VM and VDD (R_{VMD}) is the internal resistance between VM and VDD under the set conditions of $V1 = 1.8\text{ V}$ and $V2 = 0\text{ V}$.

The resistance between VM and VSS (R_{VMS}) is the internal resistance between VM and VDD under the set conditions of $V1 = 3.5\text{ V}$ and $V2 = 1.0\text{ V}$.

(7) Test Condition 7, Test Circuit 4

《 CO Pin Resistance “H”, CO Pin Resistance “L” 》

The CO pin resistance “H” (R_{COH}) is the resistance to the CO pin under the set condition of $V1 = 3.5\text{ V}$, $V2 = 0\text{ V}$ and $V3 = 3.0\text{ V}$.

The CO pin resistance “L” (R_{COL}) is the resistance to the CO pin under the set condition of $V1 = 4.5\text{ V}$, $V2 = 0\text{ V}$ and $V3 = 0.5\text{ V}$.

(8) Test Condition 8, Test Circuit 4

《 DO Pin Resistance “H”, DO Pin Resistance “L” 》

The DO pin resistance “H” (R_{DOH}) is the resistance to the DO pin under the set condition of $V1 = 3.5\text{ V}$, $V2 = 0\text{ V}$ and $V4 = 3.0\text{ V}$.

The DO pin resistance “L” (R_{DOL}) is the resistance to the DO pin under the set condition of $V1 = 1.8\text{ V}$, $V2 = 0\text{ V}$ and $V4 = 0.5\text{ V}$.

(9) Test Condition 9, Test Circuit 5

《 Overcharge Detection Delay Time, Overdischarge Detection Delay Time 》

The overcharge detection delay time (t_{CU}) is the time needed for V_{CO} to change from “H” to “L” just after the voltage $V1$ momentarily increases (within $10\text{ }\mu\text{s}$) from the overcharge detection voltage ($V_{CU} - 0.2\text{ V}$) to the overcharge detection voltage ($V_{CU} + 0.2\text{ V}$) under the set condition of $V2 = 0\text{ V}$.

The overdischarge detection delay time (t_{DL}) is the time needed for V_{DO} to change from “H” to “L” just after the voltage $V1$ momentarily decreases (within $10\text{ }\mu\text{s}$) from the overdischarge detection voltage ($V_{DL} + 0.2\text{ V}$) to the overdischarge detection voltage ($V_{DL} - 0.2\text{ V}$) under the set condition of $V2 = 0\text{ V}$.

(10) Test Condition 10, Test Circuit 5

《 Overcurrent 1 Detection Delay Time, Overcurrent 2 Detection Delay Time, Load Short-circuiting Detection Delay Time, Abnormal Charge Current Detection Delay Time 》

The overcurrent 1 detection delay time (t_{OV1}) is the time needed for V_{DO} to go “L” after the voltage $V2$ momentarily increases (within $10\text{ }\mu\text{s}$) from 0 V to 0.35 V under the set condition of $V1 = 3.5\text{ V}$ and $V2 = 0\text{ V}$.

The overcurrent 2 detection delay time (t_{OV2}) is the time needed for V_{DO} to go “L” after the voltage $V2$ momentarily increases (within $10\text{ }\mu\text{s}$) from 0 V to 0.7 V under the set condition of $V1 = 3.5\text{ V}$ and $V2 = 0\text{ V}$.

The load short-circuiting detection delay time (t_{SHORT}) is the time needed for V_{DO} to go “L” after the voltage $V2$ momentarily increases (within $10\text{ }\mu\text{s}$) from 0 V to 1.6 V under the set condition of $V1 = 3.5\text{ V}$ and $V2 = 0\text{ V}$.

The abnormal charge current detection delay time is the time needed for V_{CO} to go from “H” to “L” after the voltage $V2$ momentarily decreases (within $10\text{ }\mu\text{s}$) from 0 V to -1.1 V under the set condition of $V1 = 3.5\text{ V}$ and $V2 = 0\text{ V}$. The abnormal charge current detection delay time has the same value as the overcharge detection delay time.

(11) Test Condition 11, Test Circuit 2 (Product with 0 V battery charge function)

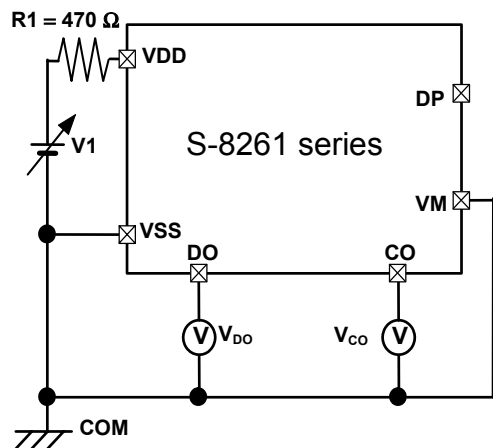
《 0 V Battery Charge Starting Charger Voltage 》

The 0 V battery charge starting charger voltage (V_{OCHA}) is defined as the voltage between VDD and VM at which V_{CO} goes “H” ($V_{VM} + 0.1\text{ V}$ or higher) when the voltage $V2$ is gradually decreased from the starting condition of $V1 = V2 = 0\text{ V}$.

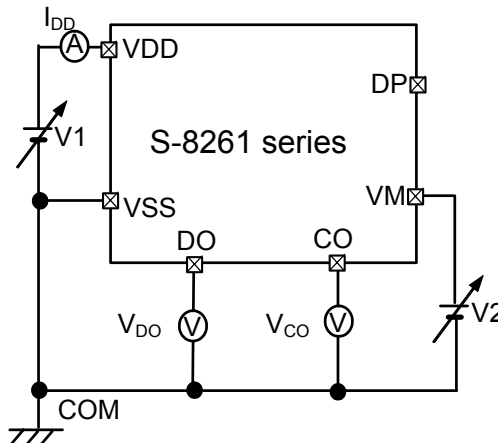
(12) Test Condition 12, Test Circuit 2 (Product with 0 V battery charge inhibition function)

《 0 V Battery Charge Inhibition Battery Voltage 》

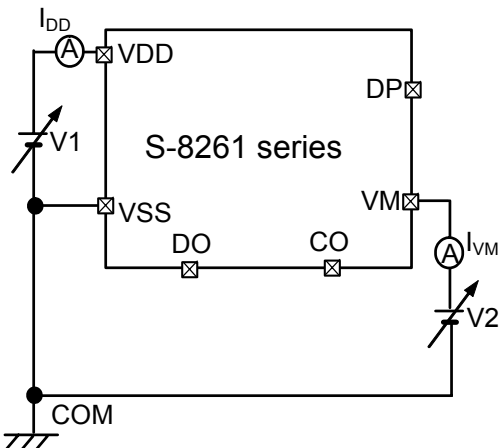
The 0 V battery charge inhibition battery voltage (V_{0INH}) is defined as the voltage between VDD and VSS at which V_{CO} goes “H” ($V_{VM} + 0.1$ V or higher) when the voltage $V1$ is gradually increased from the starting condition of $V1 = 0$ V and $V2 = -4$ V.



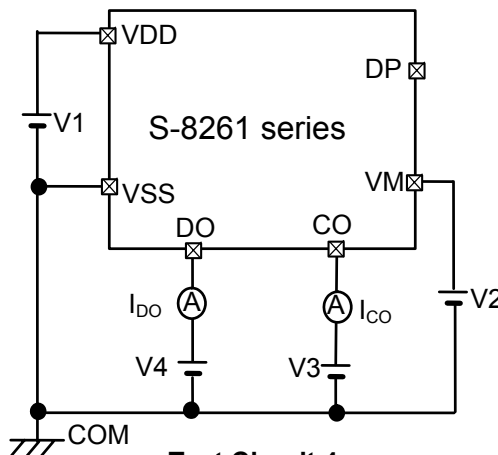
Test Circuit 1



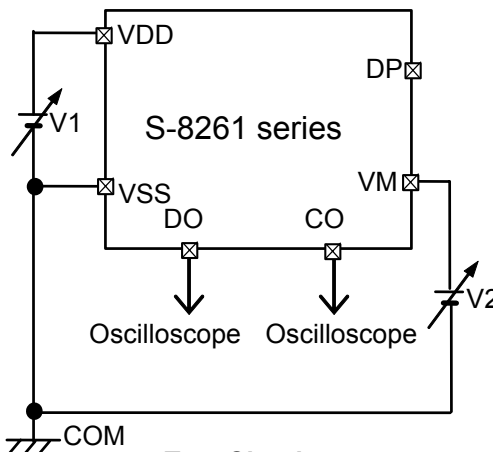
Test Circuit 2



Test Circuit 3



Test Circuit 4



Test Circuit 5

Figure 5

■ Operation

Remark Refer to the “**Battery Protection IC Connection Example**”.

1. Normal Condition

The S-8261 Series monitors the voltage of the battery connected between VDD pin and VSS pin and the voltage difference between VM pin and VSS pin to control charging and discharging. When the battery voltage is in the range from the overdischarge detection voltage (V_{DL}) to the overcharge detection voltage (V_{CU}), and the VM pin voltage is in the range from the charger detection voltage (V_{CHA}) to the overcurrent 1 detection voltage (V_{IOV1}), the IC turns both the charging and discharging control FETs on. This condition is called the normal condition, and in this condition charging and discharging can be carried out freely.

Remark When a battery is connected to the IC for the first time, discharging may not be enabled. In this case, short the VM pin and VSS pin or connect the charger to restore the normal condition.

2. Overcurrent Condition (Detection of Overcurrent 1, Overcurrent 2 and Load Short-circuiting)

When a battery in the normal status is in the status where the voltage of the VM pin is equal to or higher than the overcurrent detection voltage because the discharge current is higher than the specified value and the status lasts for the overcurrent detection delay time, the discharge control FET is turned off and discharging is stopped. This status is called the overcurrent status.

In the overcurrent status, the VM and VSS pins are shorted by the resistor between VM and VSS (R_{VMS}) in the IC. However, the voltage of the VM pin is at the V_{DD} potential due to the load as long as the load is connected. When the load is disconnected, the VM pin returns to the V_{SS} potential.

This IC detects the status when the impedance between the EB+ pin and EB- pin (Refer to **Figure 11**) increases and is equal to the impedance that enables automatic restoration and the voltage at the VM pin returns to overcurrent detection voltage 1 (V_{IOV1}) or lower and the overcurrent status is restored to the normal status.

Remark The impedance that enables automatic restoration varies depending on the battery voltage and the set value of overcurrent 1 detection voltage.

3. Overcharge Condition

When the battery voltage becomes higher than the overcharge detection voltage (V_{CU}) during charging under the normal condition and the detection continues for the overcharge detection delay time (t_{CU}) or longer, the S-8261 Series turns the charging control FET off to stop charging. This condition is called the overcharge condition.

The overcharge condition is released by the following two cases ((1) and (2)):

- (1) When the battery voltage falls below the overcharge release voltage (V_{CU}) – overcharge detection hysteresis voltage (V_{HC}), the S-8261 Series turns the charging control FET on and turns to the normal condition.
- (2) When a load is connected and discharging starts, the S-8261 Series turns the charging control FET on and returns to the normal condition. Just after the load is connected and discharging starts, the discharging current flows through the parasitic diode in the charging control FET. At this moment the VM pin potential becomes V_f , the voltage for the parasitic diode, higher than V_{SS} level. When the battery voltage goes under the overcharge detection voltage (V_{CU}) and provided that the VM pin voltage is higher than the overcurrent 1 detection voltage, the S-8261 Series releases the overcharge condition.

Remark 1. If the battery is charged to a voltage higher than the overcharge detection voltage (V_{CU}) and the battery voltage does not fall below the overcharge detection voltage (V_{CU}) even when a heavy load is connected, the detection of overcurrent 1, overcurrent 2 and load short-circuiting do not function until the battery voltage falls below over charge detection voltage (V_{CU}). Since an actual battery has an internal impedance of several dozens of $m\Omega$, the battery voltage drops immediately after a heavy load that causes overcurrent is connected, and the detection of overcurrent 1, overcurrent 2 and load short-circuiting function.

2. When a charger is connected after the overcharge detection, the overcharge condition is not released even if the battery voltage is below the overcharge release voltage (V_{CL}). The overcharge condition is released when the VM pin voltage goes over the charger detection voltage (V_{CHA}) by removing the charger.

4. Overdischarge Condition

When the battery voltage falls below the overdischarge detection voltage (V_{DL}) during discharging under the normal condition and the detection continues for the overdischarge detection delay time (t_{DL}) or longer, the S-8261 Series turns the discharging control FET off to stop discharging. This condition is called the overdischarge condition. When the discharging control FET is turned off, the VM pin voltage is pulled up by the resistor between VM and VDD in the IC (R_{VMD}). When the voltage difference between the VM and VDD then is 1.3 V (typ.) or lower, the current consumption is reduced to the power-down current consumption (I_{PDN}). This condition is called the power-down condition.

The power-down condition is released when a charger is connected and the voltage difference between the VM and VDD becomes 1.3 V (typ.) or higher. Moreover when the battery voltage becomes the overdischarge detection voltage (V_{DL}) or higher, the S-8261 Series turns the discharging FET on and returns to the normal condition.

5. Charger Detection

When a battery in the overdischarge condition is connected to a charger and provided that the VM pin voltage is lower than the charger detection voltage (V_{CHA}), the S-8261 Series releases the overdischarge condition and turns the discharging control FET on when the battery voltage becomes equal to or higher than the overdischarge detection voltage (V_{DL}) since the charger detection function works. This action is called charger detection.

When a battery in the overdischarge condition is connected to a charger and provided that the VM pin voltage is not lower than the charger detection voltage (V_{CHA}), the S-8261 Series releases the overdischarge condition when the battery voltage reaches the overdischarge detection voltage (V_{DL}) + overdischarge hysteresis (V_{HD}) or higher.

6. Abnormal Charge Current Detection

If the VM pin voltage falls below the charger detection voltage (V_{CHA}) during charging under normal condition and it continues for the overcharge detection delay time (t_{CU}) or longer, the charging control FET turns off and charging stops. This action is called the abnormal charge current detection.

Abnormal charge current detection works when the DO pin voltage is "H" and the VM pin voltage falls below the charger detection voltage (V_{CHA}). Consequently, if an abnormal charge current flows to an over-discharged battery, the S-8261 Series turns the charging control FET off and stops charging after the battery voltage becomes higher than the overdischarge detection voltage which make the DO pin voltage "H", and still after the overcharge detection delay time (t_{CU}) elapses.

Abnormal charge current detection is released when the voltage difference between VM pin and VSS pin becomes less than charger detection voltage (V_{CHA}).

7. Delay Circuits

The detection delay times are determined by dividing a clock of the approximately 3.5 kHz with the counter.

Remark 1. The detection delay time for overcurrent 2 (t_{IOV2}) and load short-circuiting (t_{SHORT}) start when the overcurrent 1 (V_{IOV1}) is detected. When the overcurrent 2 (V_{IOV2}) or load short-circuiting (V_{SHORT}) is detected over the detection delay time for each of them ($= t_{IOV2}$ or t_{SHORT}) after the detection of overcurrent 1 (V_{IOV1}), the S-8261 Series turns the FET off within t_{IOV2} or t_{SHORT} of each detection.

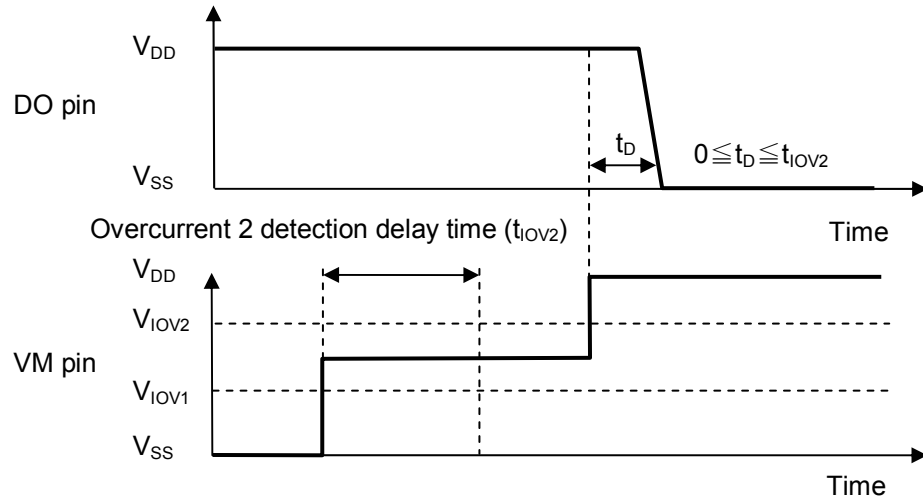


Figure 6

- When the overcurrent is detected and continues for longer than the overdischarge detection delay time (t_{DL}) without releasing the load, the condition changes to the power-down condition when the battery voltage falls below the overdischarge detection voltage (V_{DL}). When the battery voltage falls below the overdischarge detection voltage (V_{DL}) due to the overcurrent, the S-8261 Series turns the discharging control FET off by the overcurrent detection. In this case the recovery of the battery voltage is so slow that if the battery voltage after the overdischarge detection delay time (t_{DL}) is still lower than the over discharge detection voltage (V_{DL}), the S-8261 Series shifts to the power-down condition.

8. DP Pin

The DP pin is a test pin for delay time measurement and it should be open in the actual application. If a capacitor whose capacitance is larger than 1000 pF or a resistor whose resistance is less than 1 MΩ is connected to this pin, error may occur in the delay times or in the detection voltages.

9. 0 V Battery Charging Function “Available”

This function is used to recharge the connected battery whose voltage is 0 V due to the self-discharge. When the 0 V battery charge starting charger voltage (V_{0CHA}) or higher is applied between EB+ pin and EB- pin by connecting a charger, the charging control FET gate is fixed to VDD pin voltage. When the voltage between the gate and source of the charging control FET becomes equal to or higher than the turn-on voltage due to the charger voltage, the charging control FET is turned on to start charging. At this time, the discharging control FET is off and the charging current flows through the internal parasitic diode in the discharging control FET. When the battery voltage becomes equal to or higher than the overdischarge release voltage (V_{DU}), the S-8261 Series enters the normal condition.

Caution Some battery providers do not recommend charging for completely self-discharged battery. Please ask battery providers before determine whether to enable or inhibit the 0 V battery charging function.

Remark The 0 V battery charge function has higher priority than the abnormal charge current detection function. Consequently, a product with the 0 V battery charging function is enabled charges a battery forcibly and abnormal charge current cannot be detected when the battery voltage is low.

10. 0 V Battery Charging Function “Unavailable”

This function inhibits the recharging when a battery that is short-circuited (0 V battery) internally is connected. When the battery voltage is the 0 V battery charge inhibition battery voltage (V_{0INH}) or lower, the charging control FET gate is fixed to EB- pin voltage to inhibit charging. When the battery voltage is the 0 V battery charge inhibition battery voltage (V_{0INH}) or higher, charging can be performed.

Caution Some battery providers do not recommend charging for completely self-discharged battery. Please ask battery providers before determining the 0 V battery charging function.

■ **Operation Timing Chart**

1. Overcharge and Overdischarge Detection

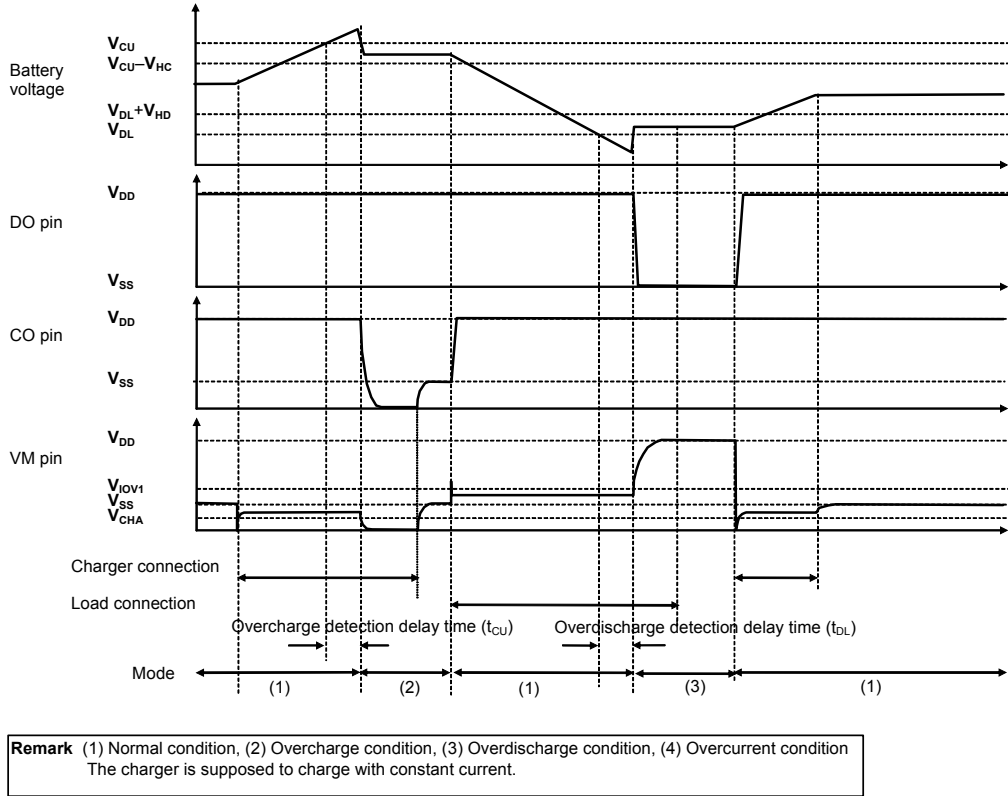


Figure 7

2. Overcurrent Detection

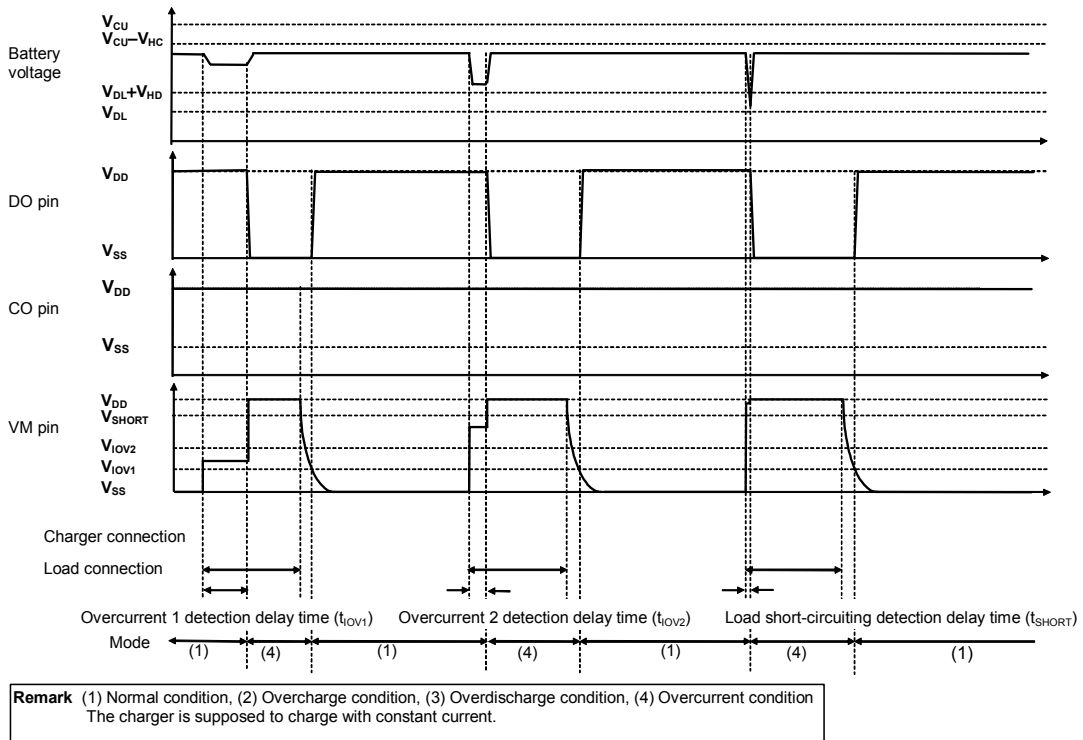
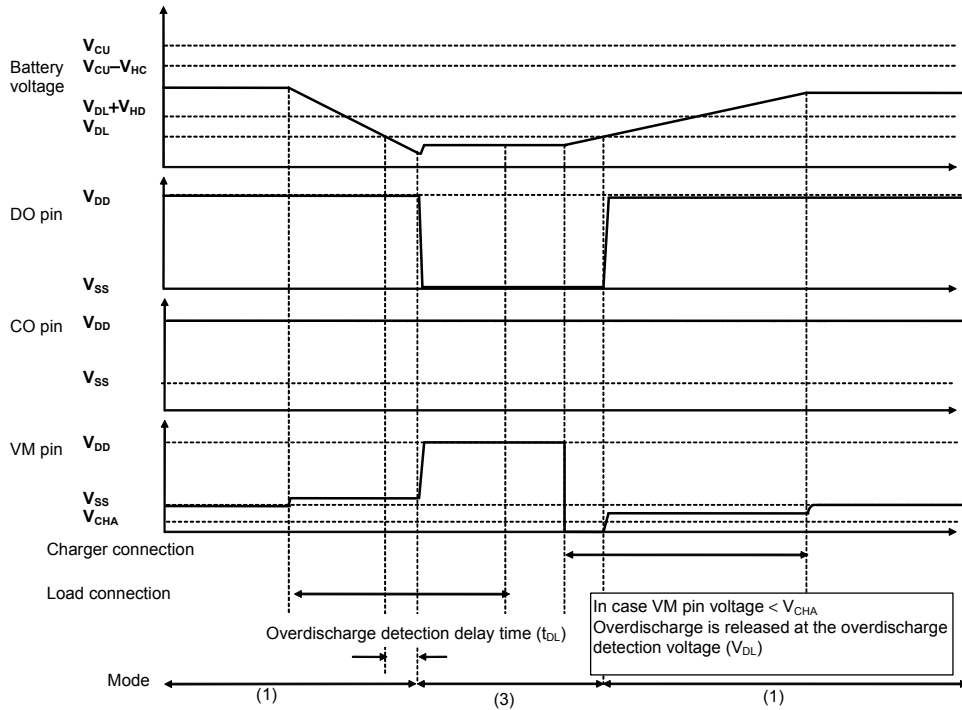


Figure 8

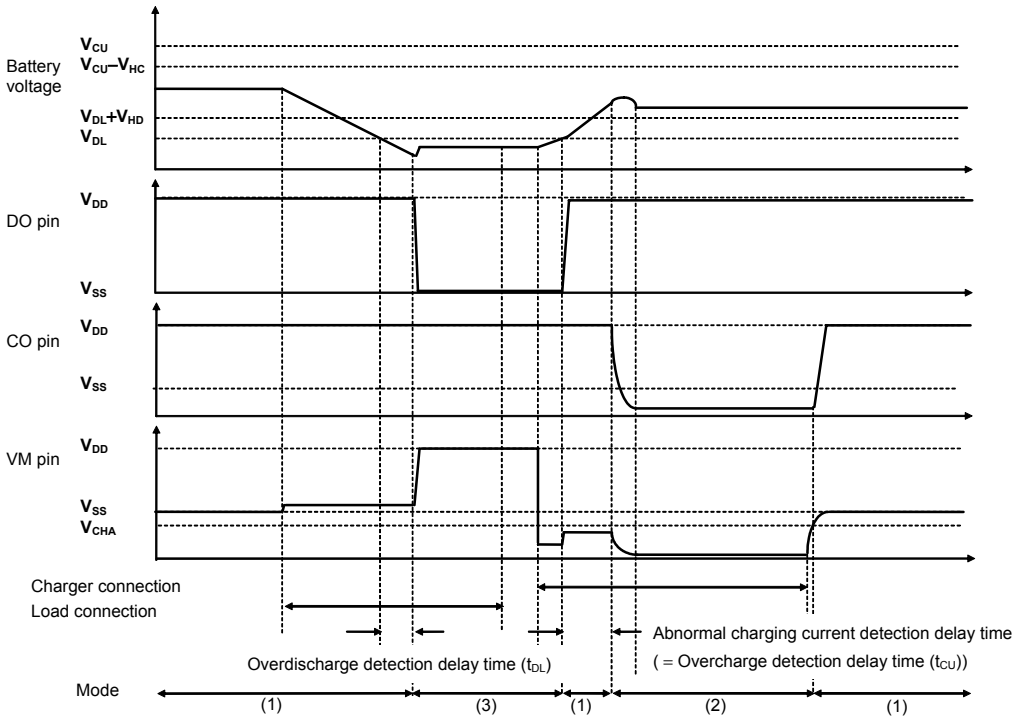
3. Charger Detection



Remark (1) Normal condition, (2) Overcharge condition, (3) Overdischarge condition, (4) Overcurrent condition
The charger is supposed to charge with constant current.

Figure 9

4. Abnormal Charge Current Detection



Remark (1) Normal condition, (2) Overcharge condition, (3) Overdischarge condition, (4) Overcurrent condition
The charger is supposed to charge with constant current.

Figure 10

■ **Battery Protection IC Connection Example**

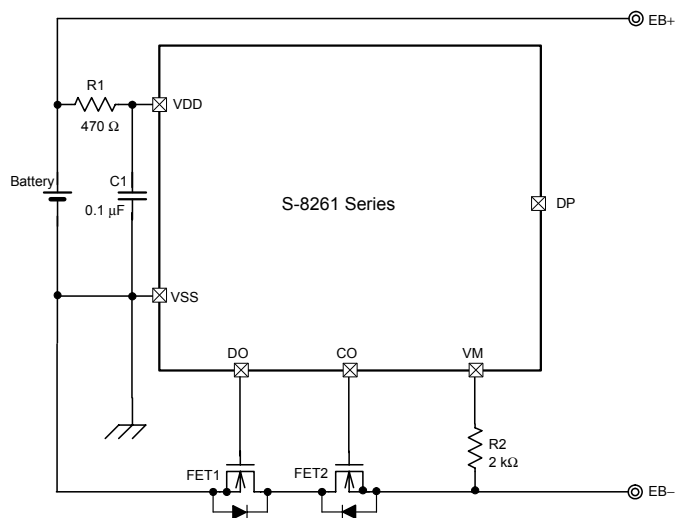


Figure 11

Table 14 Constant for External Components

Symbol	Part	Purpose	Typ.	Min.	Max.	Remarks
FET1	N-channel MOS FET	Discharge control	—	—	—	Threshold voltage \leq Overdischarge detection voltage ^{*1} Gate to source withstanding voltage \geq Charger voltage ^{*2}
FET2	N-channel MOS FET	Charge control	—	—	—	Threshold voltage \leq Overdischarge detection voltage ^{*1} Gate to source withstanding voltage \geq Charger voltage ^{*2}
R1	Resistor	ESD protection, For power fluctuation	470 Ω	300 Ω	1 k Ω	Resistance should be as small as possible to avoid lowering of the overcharge detection accuracy caused by VDD pin current. ^{*3}
C1	Capacitor	For power fluctuation	0.1 μ F	0.022 μ F	1.0 μ F	Install a capacitor of 0.022 μ F or higher between VDD and VSS. ^{*4}
R2	Resistor	Protection for reverse connection of a charger	2 k Ω	300 Ω	4 k Ω	Select as large a resistance as large as possible to prevent current when a charger is connected in reverse. ^{*5}

- *1. If the threshold voltage of an FET is low, the FET may not cut the charging current.
If an FET with a threshold voltage equal to or higher than the overdischarge detection voltage is used, discharging may be stopped before overdischarge is detected.
- *2. If the withstanding voltage between the gate and source is lower than the charger voltage, the FET may be destroyed.
- *3. If R1 has a high resistance, the voltage between VDD and VSS may exceed the absolute maximum rating when a charger is connected in reverse since the current flows from the charger to the IC. Insert a resistor of 300 Ω or higher to R1 for ESD protection.
- *4. If a capacitor of less than 0.022 μ F is connected to C1, DO may oscillate when load short-circuiting is detected. Be sure to connect a capacitor of 0.022 μ F or higher to C1.
- *5. If R2 has a resistance higher than 4 k Ω , the charging current may not be cut when a high-voltage charger is connected.

- Caution**
1. The above constants may be changed without notice.
 2. The DP pin should be open.
 3. It has not been confirmed whether the operation is normal or not in circuits other than the above example of connection. In addition, the example of connection shown above and the constant do not guarantee proper operation. Perform through evaluation using the actual application to set the constant.

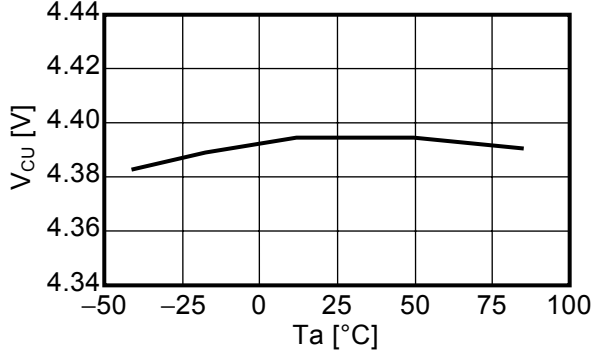
■ **Precautions**

- The application conditions for the input voltage, output voltage, and load current should not exceed the package power dissipation.
- Do not apply an electrostatic discharge to this IC that exceeds the performance ratings of the built-in electrostatic protection circuit.
- SII claims no responsibility for any and all disputes arising out of or in connection with any infringement by products including this IC of patents owned by a third party.

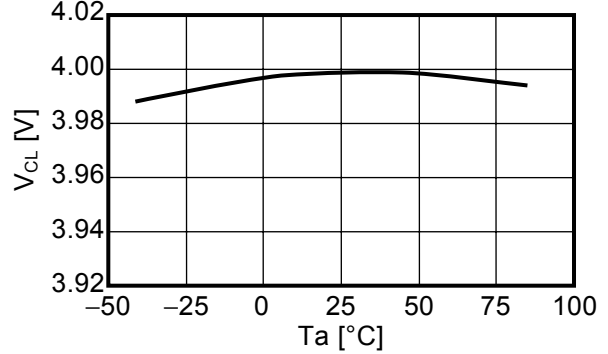
■ **Characteristics (Typical Data)**

1. Detection / Release Voltage Temperature Characteristics

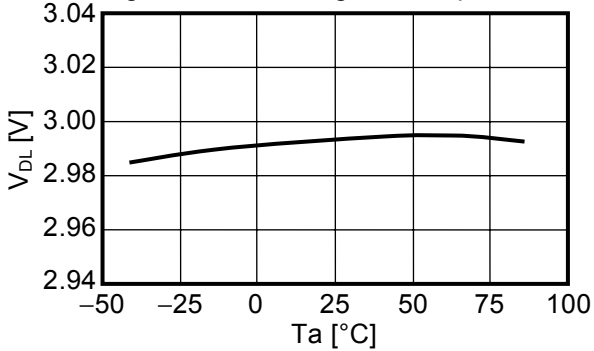
Overcharge detection voltage vs. temperature



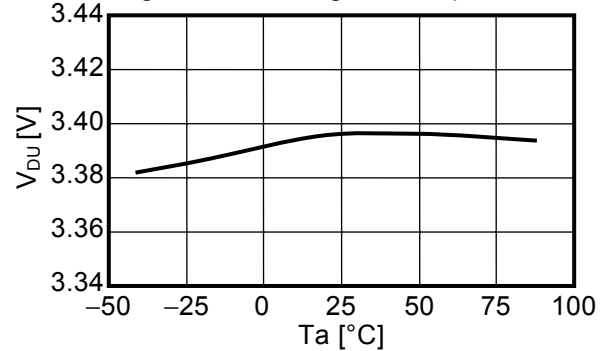
Overcharge release voltage vs. temperature



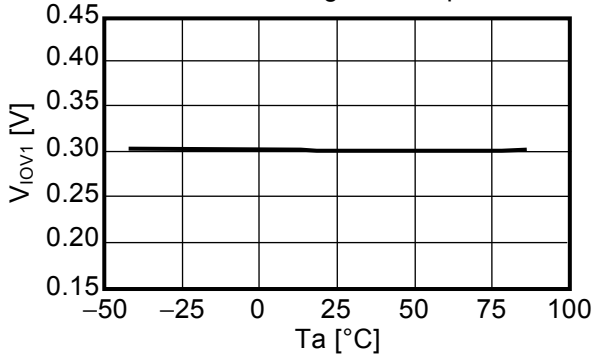
Overdischarge detection voltage vs. temperature



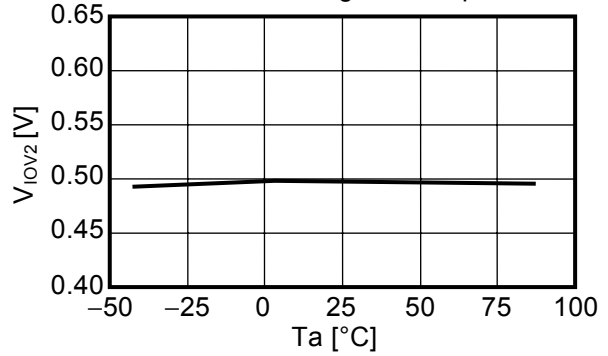
Overdischarge release voltage vs. temperature



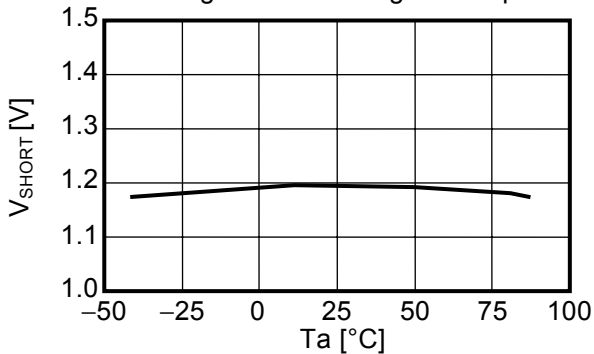
Overcurrent 1 detection voltage vs. temperature



Overcurrent 2 detection voltage vs. temperature

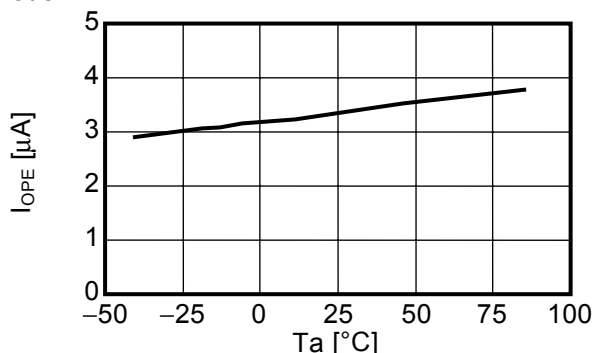


Load short-circuiting detection voltage vs. temperature

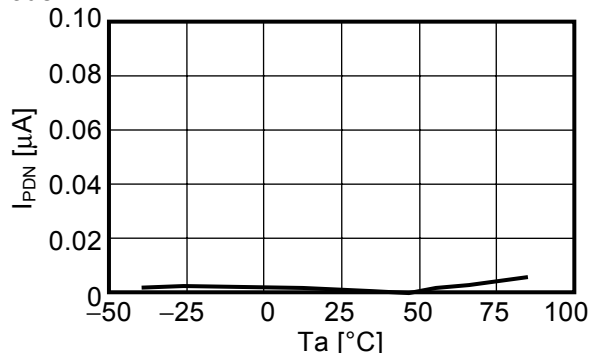


2. Current Consumption Temperature Characteristics

Current consumption vs. temperature in normal mode

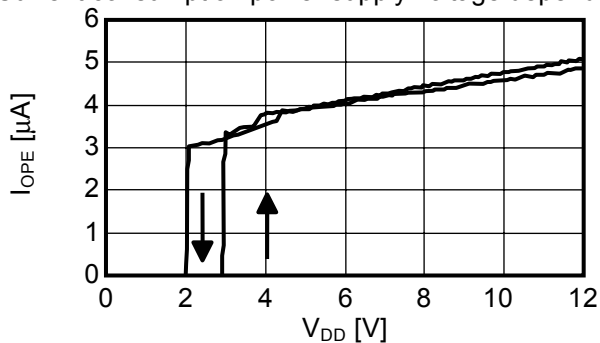


Current consumption vs. temperature in power-down mode



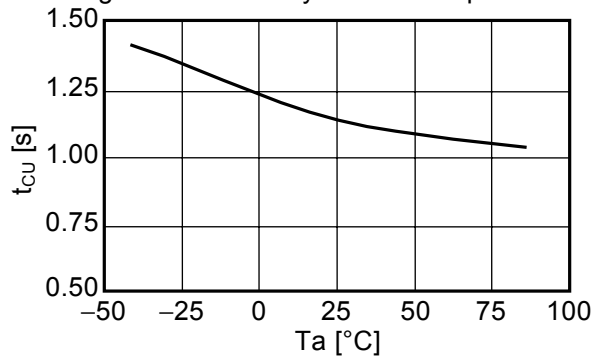
3. Current Consumption Power Voltage Characteristics (Ta=25°C)

Current consumption power supply voltage dependency

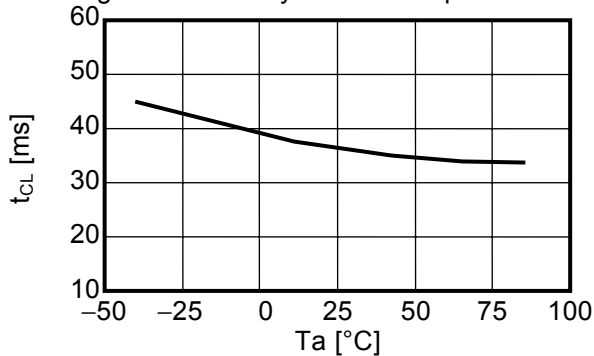


4. Detection / Release Delay Time Temperature Characteristics

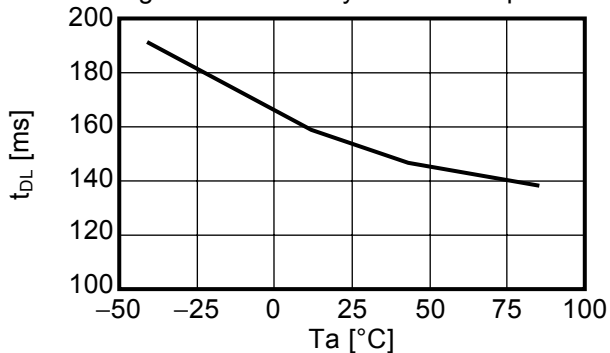
Overcharge detection delay time vs. temperature



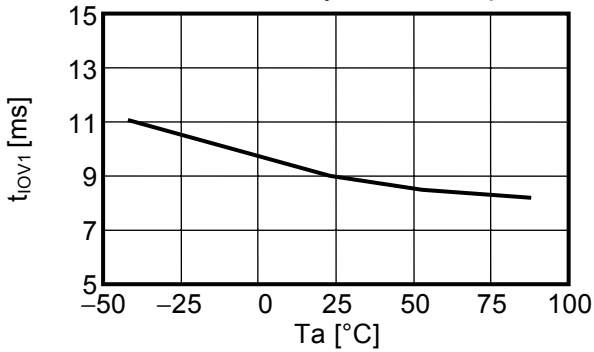
Overcharge release delay time vs. temperature



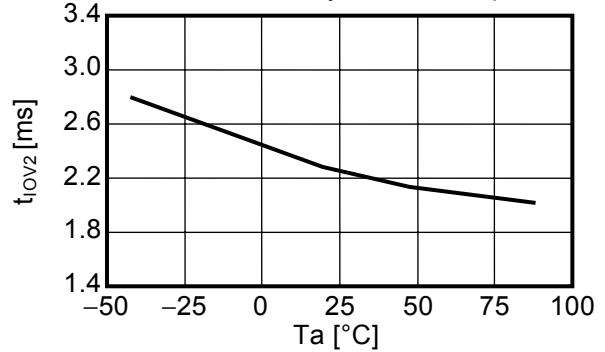
Overdischarge detection delay time vs. temperature



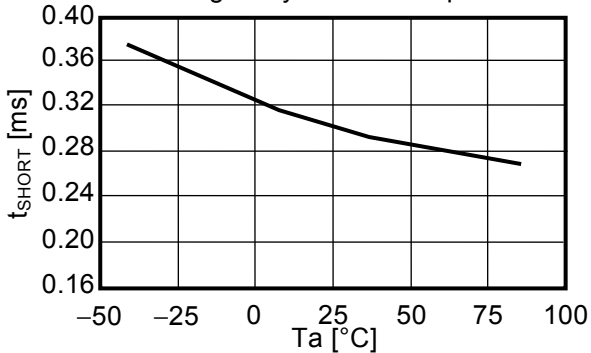
Overcurrent 1 detection delay time vs. temperature



Overcurrent 2 detection delay time vs. temperature

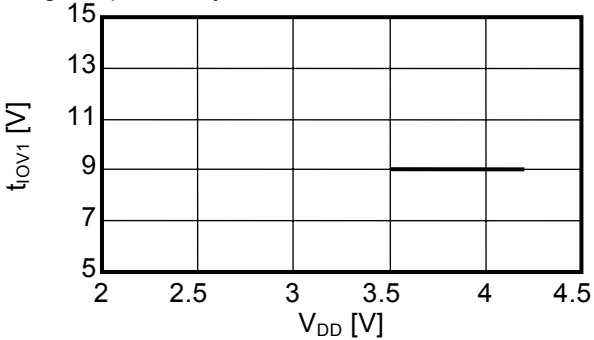


Load short-circuiting delay time vs. temperature

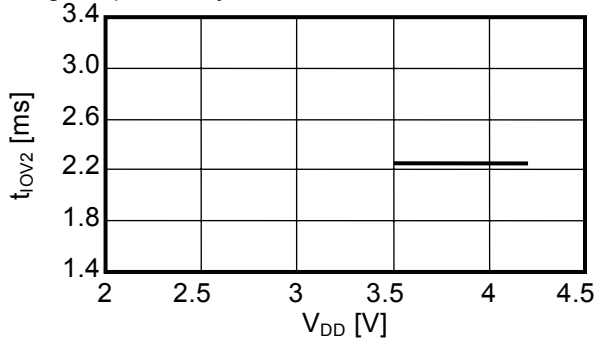


5. Delay Time Power-Voltage Characteristics (Ta=25°C)

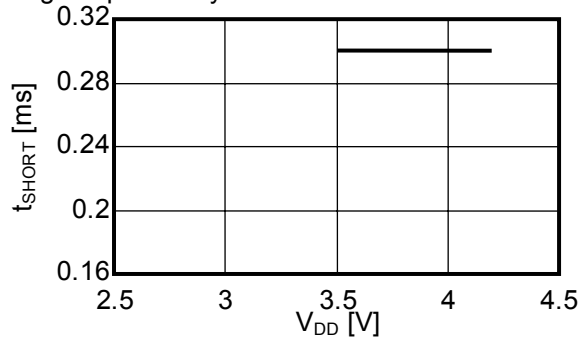
Overcurrent 1 detection delay time vs. power supply voltage dependency



Overcurrent 2 detection delay time vs. power supply voltage dependency



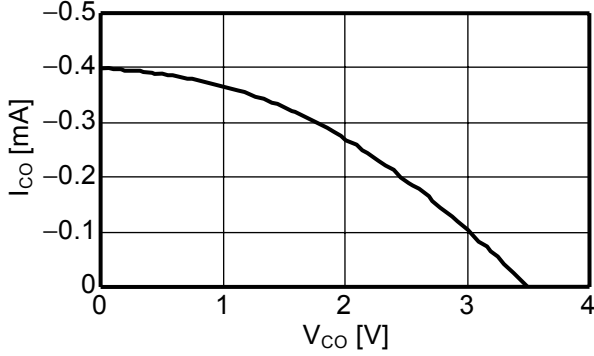
Load short-circuiting delay time vs. power supply voltage dependency



6. CO Pin / DO Pin Output Current Characteristics (Ta = 25°C)

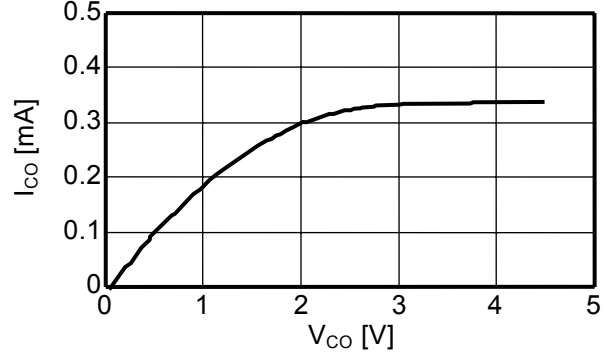
CO pin source current characteristics

$V_{DD} = 3.5\text{ V}, V_M = V_{SS} = 0\text{ V}$



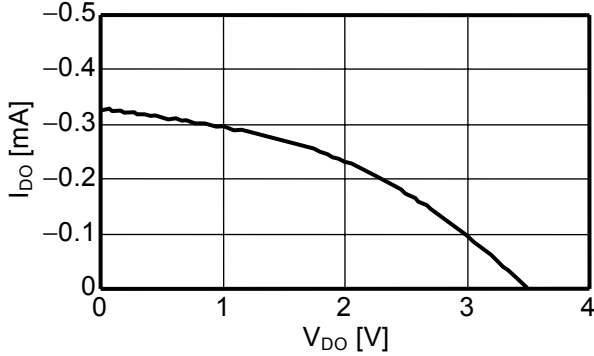
CO pin sink current characteristics

$V_{DD} = 4.5\text{ V}, V_M = V_{SS} = 0\text{ V}$



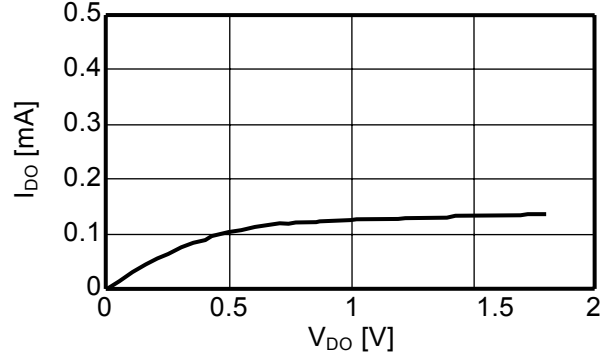
DO pin source current characteristics

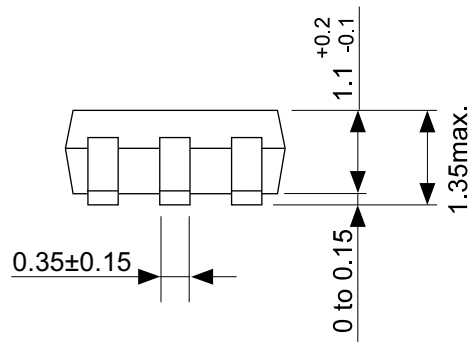
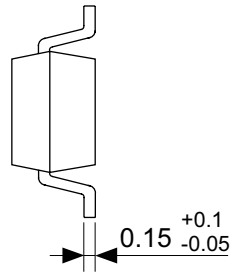
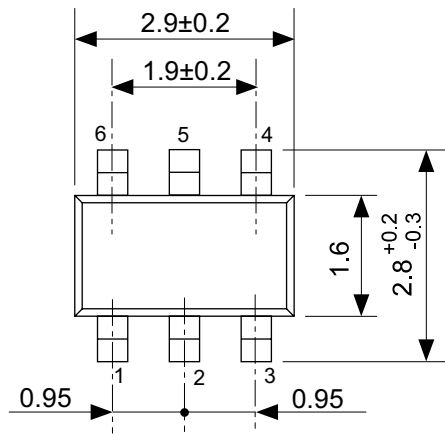
$V_{DD} = 3.5\text{ V}, V_M = V_{SS} = 0\text{ V}$



DO pin sink current characteristics

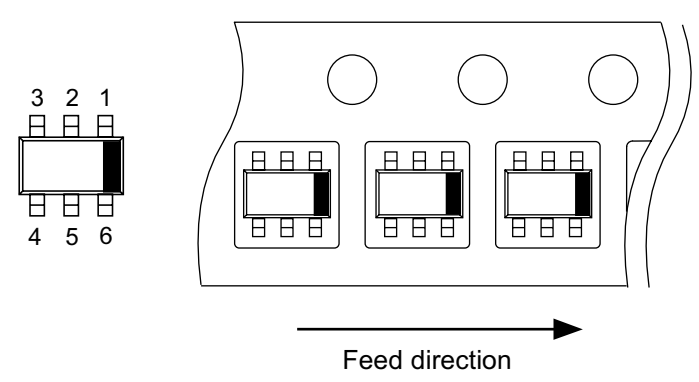
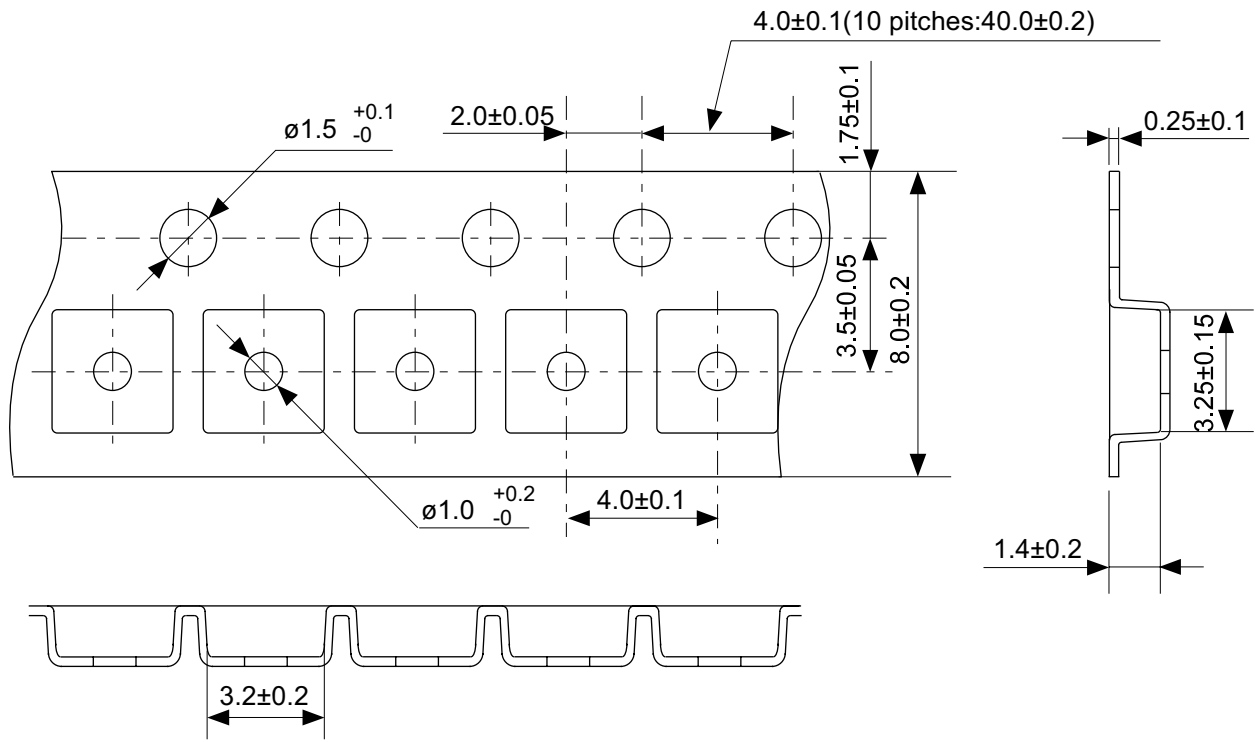
$V_{DD} = 1.8\text{ V}, V_M = V_{SS} = 0\text{ V}$





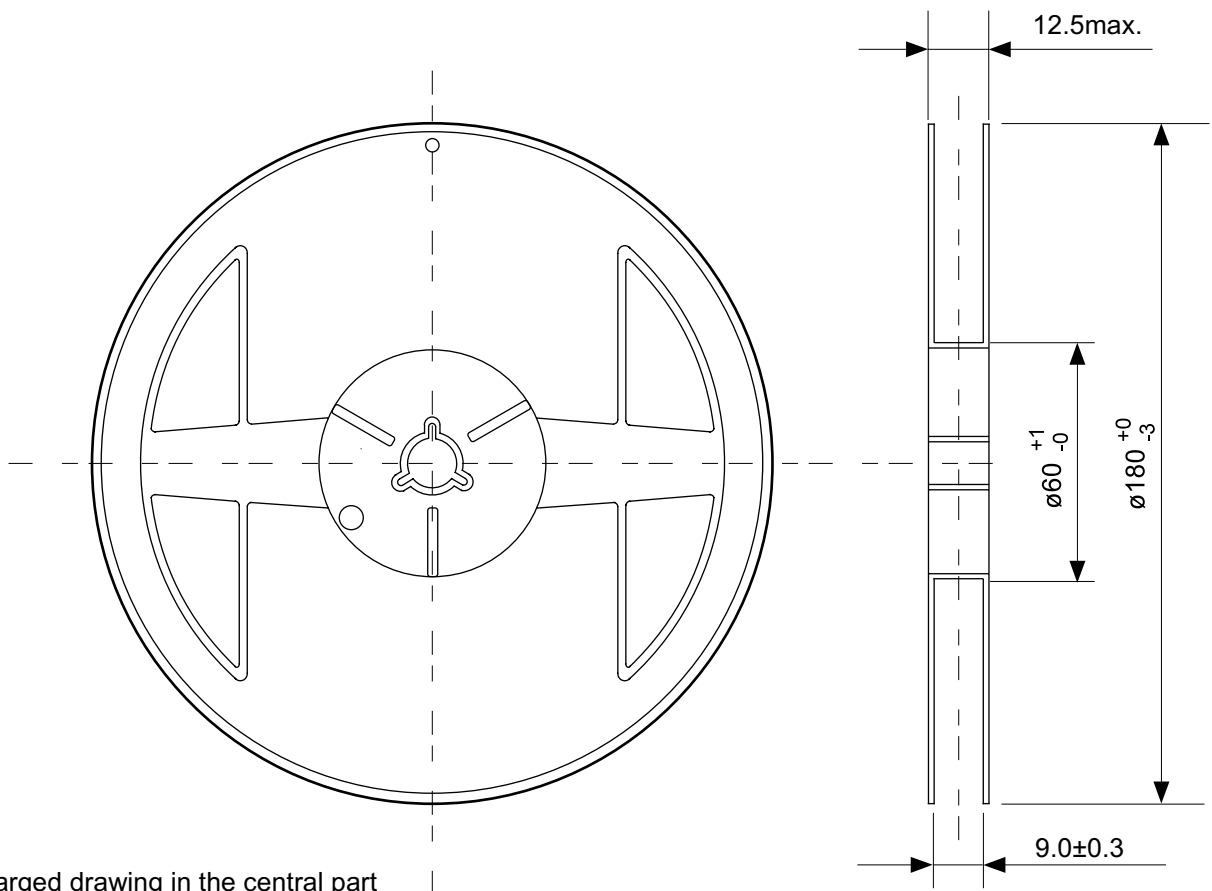
No. MP006-A-P-SD-1.1

TITLE	SOT236-A-PKG Dimensions
No.	MP006-A-P-SD-1.1
SCALE	
UNIT	mm
Seiko Instruments Inc.	

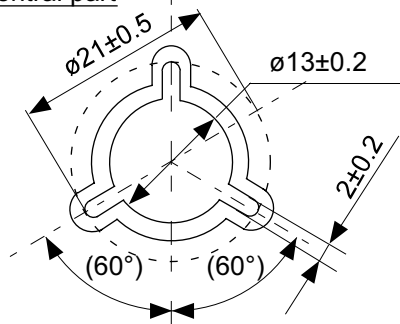


No. MP006-A-C-SD-3.1

TITLE	SOT236-A-Carrier Tape
No.	MP006-A-C-SD-3.1
SCALE	
UNIT	mm
Seiko Instruments Inc.	

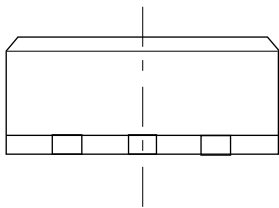
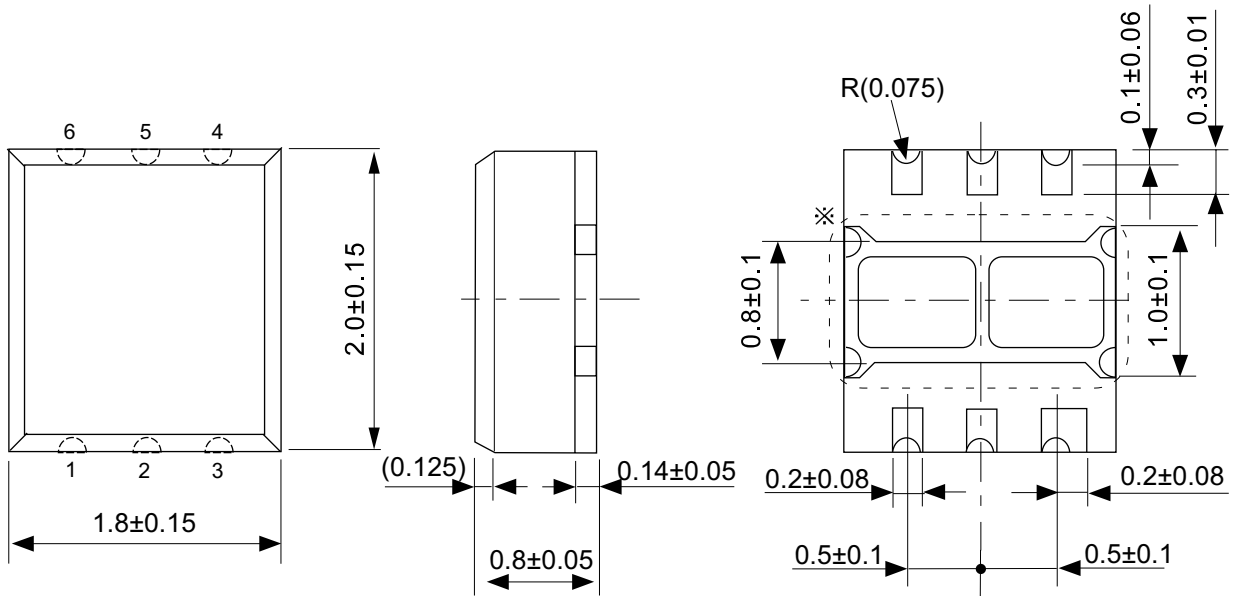


Enlarged drawing in the central part



No. MP006-A-R-SD-2.1

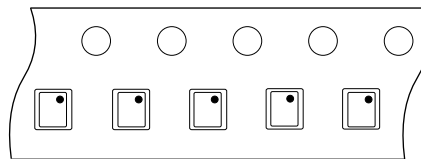
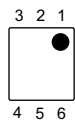
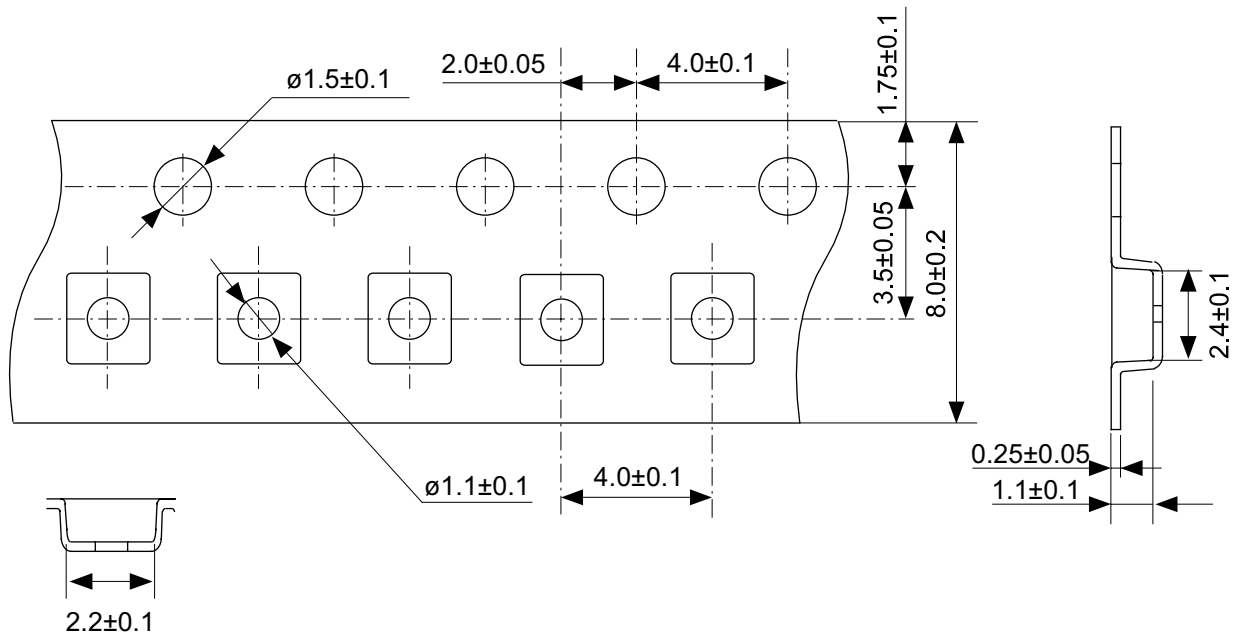
TITLE	SOT236-A-Reel		
No.	MP006-A-R-SD-2.1		
SCALE		QTY	3,000
UNIT	mm		
Seiko Instruments Inc.			



※ The heatsink of back side has different electric potential depending on the product.
 Confirm specifications of each product.
 Do not use it as the function of electrode.

No. BD006-A-P-SD-3.0

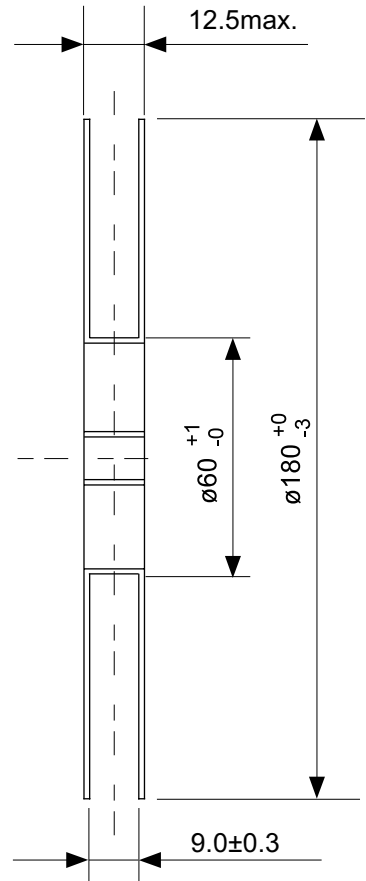
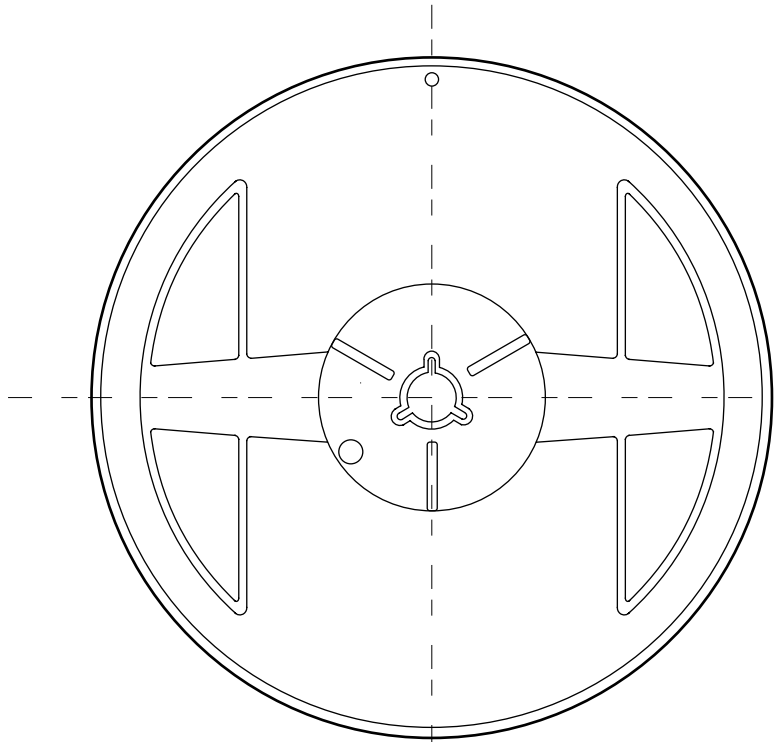
TITLE	SNB6B-A-PKG Dimensions
No.	BD006-A-P-SD-3.0
SCALE	
UNIT	mm
Seiko Instruments Inc.	



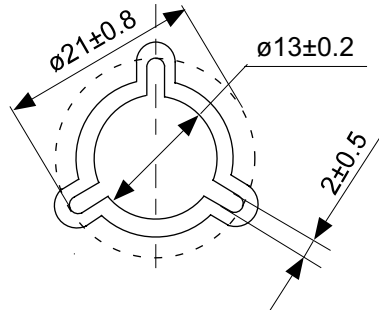
Feed direction →

No. BD006-A-C-SD-2.1

TITLE	SNB6B-A-Carrier Tape
No.	BD006-A-C-SD-2.1
SCALE	
UNIT	mm
Seiko Instruments Inc.	



Enlarged drawing in the central part



No. BD006-A-R-SD-1.1

TITLE	SNB6B-A-Reel		
No.	BD006-A-R-SD-1.1		
SCALE		QTY.	3,000
UNIT	mm		

Seiko Instruments Inc.

- The information described herein is subject to change without notice.
- Seiko Instruments Inc. is not responsible for any problems caused by circuits or diagrams described herein whose related industrial properties, patents, or other rights belong to third parties. The application circuit examples explain typical applications of the products, and do not guarantee the success of any specific mass-production design.
- When the products described herein are regulated products subject to the Wassenaar Arrangement or other agreements, they may not be exported without authorization from the appropriate governmental authority.
- Use of the information described herein for other purposes and/or reproduction or copying without the express permission of Seiko Instruments Inc. is strictly prohibited.
- The products described herein cannot be used as part of any device or equipment affecting the human body, such as exercise equipment, medical equipment, security systems, gas equipment, or any apparatus installed in airplanes and other vehicles, without prior written permission of Seiko Instruments Inc.
- Although Seiko Instruments Inc. exerts the greatest possible effort to ensure high quality and reliability, the failure or malfunction of semiconductor products may occur. The user of these products should therefore give thorough consideration to safety design, including redundancy, fire-prevention measures, and malfunction prevention, to prevent any accidents, fires, or community damage that may ensue.